

DIALOG(R)File 345:Inpadoc/Fam.& Legal Stat

(c) 2003 EPO. All rts. reserv.

13172412

Basic Patent (No,Kind,Date): JP 8194205 A2 960730 <No. of Patents: 001>

ACTIVE MATRIX TYPE DISPLAY DEVICE (English)

Patent Assignee: TOKYO SHIBAURA ELECTRIC CO

Author (Inventor): MOTAI TOMONOBU; SUZUKI KOHEI

IPC: *G02F-001/133; G02F-001/1343; G09G-003/36

Derwent WPI Acc No: *G 96-398262; G 96-398262

Language of Document: Japanese

Patent Family:

Patent No	Kind	Date	Applic No	Kind	Date
JP 8194205	A2	960730	JP 955742	A	950118 (BASIC)

Priority Data (No,Kind,Date):

JP 955742 A 950118

BEST AVAILABLE COPY

DIALOG(R)File 347:JAPIO

(c) 2003 JPO & JAPIO. All rts. reserv.

05238705 **Image available**

ACTIVE MATRIX TYPE DISPLAY DEVICE

PUB. NO.: 08-194205 [JP 8194205 A]

PUBLISHED: July 30, 1996 (19960730)

INVENTOR(s): MOTAI TOMONOBU
 SUZUKI KOHEI

APPLICANT(s): TOSHIBA CORP [000307] (A Japanese Company or Corporation), JP
 (Japan)

APPL. NO.: 07-005742 [JP 955742]

FILED: January 18, 1995 (19950118)

INTL CLASS: [6] G02F-001/133; G02F-001/1343; G09G-003/36

JAPIO CLASS: 29.2 (PRECISION INSTRUMENTS -- Optical Equipment); 44.9
 (COMMUNICATION -- Other)

JAPIO KEYWORD: R004 (PLASMA); R011 (LIQUID CRYSTALS)

ABSTRACT

PURPOSE: To provide an active matrix type liquid crystal display device with which the reduction of the electric power consumption of a driver IC is possible.

CONSTITUTION: This active matrix type liquid crystal display device has pixel electrodes 2 which are arranged in a matrix form on a first substrate, scanning lines 3 which are arranged in the horizontal direction between these pixel electrodes 2, signal lines 4 which are arranged in the vertical direction between the pixel electrodes 2, memory elements 6 of a static type which are respectively arranged in the respective intersected parts of the scanning lines 3 and the signal lines 4 and hold the binary display signals from the signal lines 4 according to the scanning signals from the scanning lines 3, switching elements 7 which are connected at one-side terminals to the pixel electrodes 2 and at their other-side terminals to wirings 5 applying reference potential and are turned on and off by the signals held in these memory elements 6, a second substrate which is arranged to face the first substrate and is provided with counter electrodes 8 so as to face the pixel electrodes 2 and a liquid crystal layer 10 which is disposed between the first and second substrates.

(19) 日本国特許庁 (J P)

(12) 公開特許公報 (A)

(11) 特許出願公開番号

特開平8-194205

(43) 公開日 平成8年(1996)7月30日

(51) Int.Cl. ⁶	識別記号	庁内整理番号	F I	技術表示箇所
G 0 2 F 1/133	5 5 0			
	1/1343			
G 0 9 G 3/36				

審査請求 未請求 請求項の数 3 O L (全 11 頁)

(21) 出願番号 特願平7-5742

(22) 出願日 平成7年(1995)1月18日

(71) 出願人 000003078

株式会社東芝

神奈川県川崎市幸区堀川町72番地

(72) 発明者 ▲もたい▼ 友智

神奈川県横浜市磯子区新磯子町33番地 株式会社東芝生産技術研究所内

(72) 発明者 鈴木 公平

神奈川県横浜市磯子区新磯子町33番地 株式会社東芝生産技術研究所内

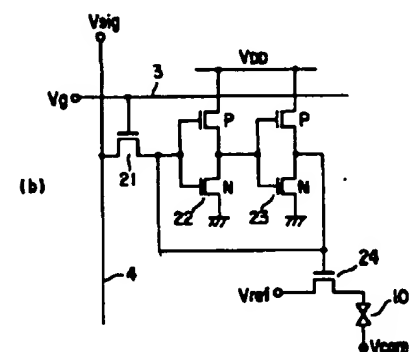
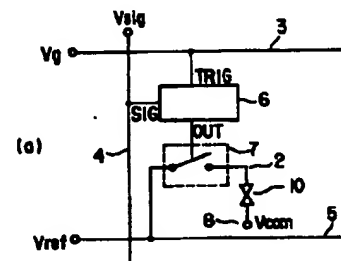
(74) 代理人 弁理士 鈴木 武彦

(54) 【発明の名称】 アクティブマトリックス型表示装置

(57) 【要約】

【目的】 ドライバICの消費電力を低減することのできるアクティブマトリックス型液晶表示装置を提供することにある。

【構成】 アクティブマトリックス型液晶表示装置において、第1の基板上にマトリックス状に配置された画素電極2と、画素電極2間に横列方向に配置された走査線3と、画素電極2間に縦列方向に配置された信号線4と、走査線3と信号線4の各交差部にそれぞれ配置され、走査線3からの走査信号に応じて信号線4からの2値表示信号を保持するスタティック型のメモリ素子6と、一方の端子が画素電極2に他方の端子が基準電位を与える配線5に接続され、メモリ素子6に保持された信号によりオン・オフするスイッチ素子7と、第1の基板と対向配置され、画素電極2と対向するように対向電極8が設けられた第2の基板と、第1及び第2の基板間に設けられた液晶層10とを備えたことを特徴とする。



【特許請求の範囲】

【請求項1】第1の基板上にマトリックス状に配置された画素電極と、

第1の基板上に一方に沿って配置された複数本の走査線と、

第1の基板上に前記走査線と交差する方向に配置された複数本の信号線と、

前記走査線と前記信号線との各交差部にそれぞれ配置され、前記走査線より入力された走査信号に応じて前記信号線より入力される2値表示信号を保持するスタティック型のメモリ素子と、

これらのメモリ素子に対応してそれぞれ設けられ、一方の端子が前記画素電極に接続され、他方の端子が基準電位を与える配線に接続され、前記メモリ素子に保持された信号により端子間をオン・オフするスイッチ素子と、第1の基板と対向配置され、前記画素電極と対向するように対向電極が設けられた第2の基板と、

第1及び第2の基板間に設けられた表示材料層と、を具備してなることを特徴とするアクティブマトリックス型表示装置。

【請求項2】前記表示材料層は液晶であり、前記基準電位を与える配線及び対向電極の少なくとも一方に交流信号を印加することを特徴とする請求項1記載のアクティブマトリックス型表示装置。

【請求項3】基板上にマトリックス状に配置された画素電極と、前記基板上に一方に沿って配置された複数本の走査線と、前記基板上に前記走査線と交差する方向に配置された複数本の信号線と、前記走査線と前記信号線との各交差部に配置され、前記走査線より入力された走査信号に応じて前記信号線より入力される表示信号を保持するメモリ素子と、これらのメモリ素子に対応してそれぞれ設けられ、一方の端子が前記画素電極に接続され、他方の端子が基準電位を与える配線に接続され、前記メモリ素子に保持された信号により端子間抵抗値が変化するスイッチ素子とを具備してなり、前記画素電極が所定数毎にブロック化され、該ブロック内の画素電極の寸法がそれぞれ異なっていることを特徴とするアクティブマトリックス型表示装置。

【発明の詳細な説明】

【0001】

【産業上の利用分野】本発明は、液晶ディスプレイなどの画像表示装置に係わり、特に薄膜トランジスタ等のスイッチ素子を用いたアクティブマトリックス型表示装置に関する。

【0002】

【従来の技術】近年、液晶ディスプレイ等の薄型の表示装置の開発が活発に行われている。なかでも、どこでも持ち運べる携帯用や大画面の表示への要求が高まっており、軽量化、使用時間の長時間化、低消費電力化が求められている。このためには、電源用バッテリーの高性能

化のほかに、表示装置自体の消費電力を下げる方法による効果大きい。

【0003】液晶表示装置では、背面照明として利用されている蛍光管、導光板、蛍光管用インバータの効率が低く、現状はこれら照明で消費される電力に対する高効率化による効果が大きいことから、表示材料或いは表示パネル自体の改良による消費電力低減の試みは殆どない。しかし、将来的には表示パネル自体の消費電力を低減することが必要と考えられる。

【0004】表示パネル自体の消費電力は、おもにドライバIC特性と表示パネルの駆動方法に依存すると考えられており、使用ドライバICの低電圧化の改良が進められている。しかし、表示画素部にTFT（薄膜トランジスタ）等のスイッチ素子を設け、画像信号を短い周期で繰り返し書き込む方法（TFT-LCD）では、ドライバICの個々の画素駆動を担当するトランジスタの消費電力を低減することは容易ではない。

【0005】表示パネル自身の消費電力は、現状の10インチクラスのTFT-LCDでは、回路系の消費電力が1.5W程度で、バックライト照明が5W程度であるが、電池動作を長時間化するためには1W未満、望ましくは小型軽量電池での駆動が可能な0.2W未満が要求されている。この消費電力の問題は、照明を伴う透過型表示装置よりも、照明を伴わない反射型表示装置で顕著となる。特に、広告用表示装置等に使用される対角50センチ以上の表示装置では、消費電力量が設置場所の制約を生じさせていた。

【0006】図11(a)は、従来のアクティブマトリックス型液晶表示装置を示す回路構成図である。薄膜工程により、走査線73、信号線74、共通配線75、3端子スイッチ素子の薄膜トランジスタ77や画素部電極などが作成され、ドライバICより走査信号と画像信号が、各々走査線73と信号線74に入力される。ここで、走査信号が入力された薄膜トランジスタ77はオン状態となり、信号線74からの画像信号が補助容量78に蓄積されると共に液晶79に伝達される。走査信号が入力されない場合には、薄膜トランジスタ77はオフ状態となるため、オン時に印加された画像信号が液晶79にそのまま保持される。

【0007】このような構造の液晶表示装置では、書き込む信号がたとえ同一の画像であっても、液晶材料を交流駆動する必要上、再度、走査信号で薄膜トランジスタをオン状態にして、画像信号を再書き込みする必要が生じる。よって、駆動信号を発生させる走査信号用・画像信号用ドライバICはたえず動作するので、電力は常に消費される。

【0008】これに対して、図11(b)に示すように、第1のスイッチ素子T1により容量性負荷C1にアナログ信号を保持することで、第2のスイッチ素子T2を動作させる方法が提案されている（J.Vanfleteren (I

DRC, 1988, p74-79))。しかし、表示画面のサイズが大きくなるにつれて、スイッチ素子T2及びこれにつながる容量負荷C2が大きくなるため、さらに保持したアナログデータに変動を生じさせないために、大容量の負荷容量C1を駆動する能力を持つスイッチ素子T1が必要となる。

【0009】例えば、設計上のC1の容量値が過度に小さい場合には、T1がオンからオフとなった時のT2へ送ったオン信号のレベル減少や、T2がオン状態となる境界電圧であるしきい値電圧が経時変動することでT2のオン抵抗の上昇が発生し、目的とする表示が達成されない。加えて、C1等の大型化は消費電力の上昇を招くこととなる。これらの設計上の問題は、本素子構成がアナログ的なサンプルホールド回路よりなっているためであり、新構成の表示装置が求められていた。

【0010】一方、アクティブマトリックス型液晶表示装置においては、面積変調によるデジタル階調表示を行う方法が提案されている。これは、画素電極を所定数毎にブロック化すると共に、ブロック内の各々の画素電極の寸法を変え、各ブロック内で表示すべき画素を選択することにより、各ブロックの表示画面面積をデジタル的に可変するものである。

【0011】しかし、従来の駆動方法では、TFTなどのスイッチ素子が持つ寄生容量によって、スイッチング時に表示性能に悪影響を及ぼす画素電位のレベルシフトが発生する。このレベルシフト量は、寄生容量と画素電極容量とのスイッチングノイズ電荷の分配比で決定され、画素電極の寸法が異なるとレベルシフト量は画素電極毎に異なり、対向電極電位の調整によっても無害化することは困難である。従って、実質的に面積階調は不可能であった。

【0012】

【発明が解決しようとする課題】このように従来、ドライバICの消費電力の低減のために、液晶等の表示材料層に信号を供給するためのスイッチ素子を走査線に直接駆動するのではなく、アナログ的なサンプルホールド回路を用いて駆動する方法が提案されているが、この方法では十分な効果は達成できなかった。

【0013】また、面積変調によるデジタル階調表示を行う例では、スイッチングノイズ電荷による画素電位のレベルシフトが発生し、このレベルシフト量は画素電極の寸法が異なると画素電極毎に異なり、対向電極電位の調整によっても無害化することは困難であり、従って実質的に面積階調は不可能であった。

【0014】本発明は、上記事情を考慮してなされたもので、その目的とするところは、ドライバICの消費電力を低減することのできるアクティブマトリックス型表示装置を提供することにある。

【0015】また、本発明の他の目的は、ドライバICの消費電力を低減することができ、かつ面積変調による

デジタル階調表示を可能としたアクティブマトリックス型表示装置を提供することにある。

【0016】

【課題を解決するための手段】上記課題を解決するために、本発明は次のような構成を採用している。即ち、本発明（請求項1）は、マトリックス配置された各画素にスイッチ素子を設けたアクティブマトリックス型表示装置において、第1の基板上にマトリックス状に配置された画素電極と、第1の基板上に一方に沿って配置された複数本の走査線と、第1の基板上に前記走査線と交差する方向に配置された複数本の信号線と、前記走査線と前記信号線との各交差部にそれぞれ配置され、走査線より入力された走査信号に応じて信号線より入力される2値表示信号を保持するスタティック型のメモリ素子と、これらのメモリ素子に対応してそれぞれ設けられ、一方の端子が前記画素電極に接続され、他方の端子が基準電位を与える配線に接続され、前記メモリ素子に保持された信号により端子間をオン・オフするスイッチ素子と、第1の基板と対向配置され、前記画素電極と対向するように対向電極が設けられた第2の基板と、第1及び第2の基板間に設けられた表示材料層とを具備してなることを特徴とする。

【0017】ここで、本発明の望ましい実施態様としては、次のものがあげられる。

- (1) 表示材料層は液晶であること。
- (2) 走査線及び信号線は、画素電極間に配置されていること。
- (3) 基準電位を与える配線及び対向電極の少なくとも一方に交流信号を印加すること。
- (4) 同一走査線に接続されたメモリ素子が走査選択される時に、配線又は対向電極から印加される交流信号を一定電位とすること。
- (5) 2値表示信号を保持するメモリ素子が不揮発性メモリにより形成されていること。
- (6) メモリ素子及びスイッチ素子は、薄膜トランジスタにより形成されていること。

【0018】また、本発明（請求項4）は、マトリックス配置された各画素にスイッチ素子を設けたアクティブマトリックス型表示装置において、基板上にマトリックス状に配置された画素電極と、前記基板上に一方に沿って配置された複数本の走査線と、前記基板上に前記走査線と交差する方向に配置された複数本の信号線と、前記走査線と前記信号線との各交差部に配置され、走査線より入力された走査信号に応じて信号線より入力される表示信号を保持するメモリ素子と、これらのメモリ素子に対応してそれぞれ設けられ、一方の端子が前記画素電極に接続され、他方の端子が基準電位を与える配線に接続され、前記メモリ素子に保持された信号により端子間抵抗値が変化するスイッチ素子とを具備してなり、前記画素電極が所定数毎にブロック化され、該ブロック内の

画素電極の寸法がそれぞれ異なっていることを特徴とする。

- (1) 表示材料層は液晶であること。
- (2) 走査線及び信号線は、画素電極間に配置されていること。
- (3) スイッチ素子は、オン・オフの2状態で動作し、複数の信号線と走査線をそれぞれ2状態の電位で駆動する駆動回路を備えていること。
- (4) メモリ素子、スイッチ素子、駆動回路は、同一基板上に形成された薄膜トランジスタから構成されていること。
- (5) メモリ素子を、応用システムの画像メモリとして用いること。

【0019】

【作用】本発明（請求項1）によれば、1画素毎に設けられたスタティック型のメモリ素子によって、その画素で表示すべき情報が次に変化するまで周期的に書き換える必要なく、その状態が保たれる。表示画素の表示情報が変化しない場合には、メモリ素子への情報の書き換えは不要であるため、走査信号や画像信号を周期的に書き加える必要がなくなり、ドライバICで消費される電力が低減される。

【0020】即ち、従来装置では容量負荷の充放電に大部分の電力が消費されていたが、本発明では、従来のように表示画像が変化しなくても交流駆動のために信号線に一定周期の極性反転された信号を印加する必要がなく、信号線を駆動する駆動回路はほぼ停止状態のためそこで消費される電力は殆ど無視できるほど小さくなる。唯一消費される電力は対向電極の交流駆動によるものとなるが、これはフリッカが視認されない程度の例えば60Hz以下の低い周波数で十分なため、消費電力は従来駆動法の100分の1から1000分の1程度にドラスティックに低減される。

【0021】また、メモリ素子としてスタティック型を用いているので、大容量の負荷容量やこれを駆動する能力を持つ大きなスイッチ素子を必要とすることはなく、この点からも消費電力の低減に有効である。さらに、液晶表示装置の場合、従来ではスイッチ素子のオフ特性或いはフリッカ視認の制約から画素への信号書き換え周期を延ばすことが難しかったが、本発明の装置では、全表示画素の書き換え周期や1画素の書き換え時間を延長することが可能となる。

【0022】また、本発明（請求項4）によれば、画素電極が所定数毎にブロック化され、そのブロック内の画素電極の寸法がそれぞれ異なっていることにより、1ブロックとして面積変調によるデジタル多階調表示が容易となる。従来の駆動法でこのように面積変調表示をしようとした場合、前述したようにスイッチングノイズ電荷による画素電位のレベルシフトが発生したが、本発明では、このスイッチングノイズ電荷によるレベルシフト

は、液晶などの光電変換部材のリーク抵抗を通じてスイッチング終了後の初期に消滅する。このため、表示性能に悪影響を及ぼすことがなく、面積変調によるデジタル多階調表示が可能である。

【0023】さらに、液晶などの光電変換部材の1画素の表示状態はオン又はオフの2状態であるため、中間調表示時でも視野角は広く、表示むらもない極めて良好な表示品位が得られる。

【0024】

【実施例】以下、本発明の実施例を、公知の半導体技術を応用した薄膜工程で形成された薄膜トランジスタを利用して作成した液晶表示装置を例として説明する。

（実施例1）図1は、本発明の第1の実施例に係わるアクティブマトリックス型液晶表示装置の基本構成を示すもので、(a)は素子構造断面図、(b)は回路構成図である。ガラス等からなる第1の基板1上に画素電極2がマトリックス状に配置されており、画素電極2間には紙面左右方向に走査線3が、上下方向に信号線4が配置されている。また、走査線3と平行に参照線5が配置されている。走査線3と信号線4の交差部に後述するメモリ素子6が設けられ、メモリ素子6と画素電極2間にはスイッチ素子7が設けられている。

【0025】基板1上には所定距離離してガラス等からなる第2の基板9が対向配置されており、基板9の対向面には対向電極8が形成されている。そして、各基板1、9間に表示材料層としての液晶層10が封入されている。なお、図中の13は走査線ドライバ、14は信号線ドライバ、15は参照線ドライバである。

【0026】図2(a)は、本実施例の1画素部構成を示す回路図である。マトリックス状に形成された走査線3と信号線4の交差部に2値データ保持メモリ素子6が接続されており、このメモリ素子6には、保持されている情報を出力する出力部が設けられている。出力部には、3端子スイッチ素子7の制御端子が接続されている。このスイッチ素子7は、参照線5と画素電極2との間の抵抗値を制御し、液晶層10のバイアス状態を調整している。

【0027】図2(a)におけるメモリ素子の例として、2段インバータを用い正帰還させた形のメモリ回路、即ちスタティック型メモリ素子が考えられる。本回路では、トランジスタのオフ特性が十分でなくアナログ信号用素子として利用不可能なトランジスタ素子で実現ができる特徴を持つ。

【0028】具体的な回路構成を、図2(b)に示す。前記図11(b)と比較して、容量C1が不要であるため、図11(b)の素子T1に対応する図2の素子21は小さくてもよい。スイッチ素子21とインバータ回路部22、23の各素子サイズは、インバータ回路部の最遅段数比nと同様な考え方で設計可能である。具体的には、素子21、22、23、24の素子サイズの比が、

1:n:n:n*nで規定した場合には $n=1\sim 10$ 、願わくば $n=2\sim 10$ が良好な設計条件である。

【0029】図3(a)(b)及び図4(a)(b)にその他のメモリ素子を使用した1画素部の回路構成例を示す。図3(a)と(b)、図4(a)と(b)は、それぞれ3端子スイッチ素子の接続位置が異なる構成例を示している。従来構造より表示画素の構成する素子数が増加するため、透過型の表示素子では光利用効率が減少するが、反射型の液晶表示装置では反射電極下にメモリ素子などを形成できるため本表示素子による光利用効率の低下は生じない。

【0030】駆動波形は、図5のように従来の液晶表示装置の駆動のように線順次駆動となる。走査線3に順次走査パルス印加し、これに同期させたメモリ素子6にスイッチ素子7の開閉を制御する信号を信号線4を通して入力する。一方、共通電極(対向電極8)には交流信号を入力する。上述の通り、液晶材料の抵抗値とスイッチ素子の抵抗値の比の条件が満足されれば、上記回路・駆動で良好な表示が可能となる。

【0031】本装置は理想上、静止画像のように表示画像に変化がなくなれば、メモリ素子6へのリフレッシュは不要である。しかし、図5のように、単純な矩形波入力による駆動では、スイッチがオン状態からオフ状態へ切り替わる時にスイッチ側の液晶電位が、交流駆動信号の高い電位か低い電位かのどちらかの電位状態に固定化されるので、液晶部に直流電圧成分が加わることとなる。よって、表示性能を向上するためには、スイッチがオフ状態へ切り替わる時の液晶電位設定のための、リフレッシュ期間を設ける必要が生じる。

【0032】最も簡単な方法として、図6(a)のように、共通電極の交流信号の間にブランキング期間を設ける方法がある。従来型のデバイスでは、図11(a)の液晶79やスイッチ素子77のリーク電流による電位低下を保証する容量78を液晶容量に並列接続しているために、信号の書き込み時間を短縮することが容易でなかった。本発明の素子では、図2(b)のように、スイッチ素子21のゲート開閉のための信号を送るのみであるために、リフレッシュの時間は従来型の素子に見られる走査時間よりも短くて済む。

【0033】また、図6(b)のように、全面素子を連続的にリフレッシュせず、リフレッシュするラインの時間を分割し、矩形信号である液晶駆動信号間に挿入することも可能である。挿入法は、一定時間で見た場合に全ライン上のメモリがリフレッシュされることが望ましいが、走査ラインの一定位置で、表示画面が変化する場合、例えば点滅表示部分が固定位置である場合には、該当する表示ラインに重みを付けてリフレッシュすることも可能である。

【0034】なお、図6(b)において、Tgはリフレッシュパルス幅、1は1回のリフレッシュライン数であ

り、1画面書き替えのためのリフレッシュ回数は、(ゲートライン数)/1で定義される。

【0035】このように本実施例によれば、1画素毎にスタティック型のメモリ素子6を設け、この素子6の記憶情報でスイッチ素子7を駆動するようにしているので、表示情報が変化しない場合には、メモリ素子7への情報の書き換えは不要である。このため、走査信号や画像信号を周期的に書き加える必要がなくなり、ドライバICで消費される電力が大幅に低減される。

【0036】また、メモリ素子6がスタティック型であることから、前記図11(b)に示した従来のように、大容量の負荷容量C1やこれを駆動する能力を持つ大きなスイッチ素子T1を必要とすることはなく、この点からも消費電力の低減に有効である。さらに、本実施例では、スイッチ素子のオフ特性或いはフリッカ視認の制約が抑制され、全表示画素の書き換え周期や1画素の書き換え時間を延長することが可能となる。

【0037】本実施例において、アモルファスシリコン薄膜を使用した10インチクラスのTFT-LCDでの消費電力試算は、表示画面を書換ええない状態で10mW、毎秒一画面の書換え状態としても30mW未満と、従来と比較して、50分の1の大幅な低消費電力化が実現できた。

(実施例2) 図7は、本発明の第2の実施例に係わるアクティブマトリックス型液晶表示装置を説明するためのもので、(a)は1画素部構成を示す回路図、(b)はメモリ素子の構造断面図である。

【0038】本実施例は、基本的には第1の実施例と同様であるが、図7(a)に示すように、メモリ素子30として書換可能な不揮発性メモリを用いている。メモリ素子30の具体的な構成は図7(b)に示す通りであり、通常の逆スタガー型TFTのゲートを2層構造としたものである。図中の31は基板、32は第1ゲート(制御ゲート)、33はゲート絶縁膜、34は第2ゲート(浮遊ゲート)、35はトンネル絶縁膜、36はa-Si等の活性層、37は保護絶縁膜、38a、38bはソース・ドレイン電極である。

【0039】書換の回数は、従来駆動のスイッチング回数の目安である 10^7 回以上の書き換え動作を満足することが理想であるが、静止画表示が主体となる表示装置であるならば、書き換え回数は100~10000分の1に減少させることが可能で本表示装置のメモリ素子として利用できる。上述のメモリ素子は、EEPROM構成となっているが、誘電体材料の電場-誘電率カーブ(D-Eカーブ)が、ヒステリシスを特性を有する材料で構成される場合も同様の表示装置が構成可能である。

【0040】具体的には、図8に示すように、ヒステリシスを有する誘電体材料をゲート絶縁膜として利用することでメモリ素子を作成し、メモリ素子に加える端子間電圧を制御することで、メモリ素子のリセット、メモリ

の信号書き込みを行う。図のように、メモリ素子に薄膜トランジスタ7を接続する方法に加えて、直接表示電極にメモリ素子の接続も駆動信号の改良により可能である。

【実施例3】第1の実施例では、Vcom（共通電極8）のみに交流信号を入力して液晶材料を駆動しているが、交流信号はVref（参照線5）側に入力してもよい。Vrefに交流信号を入力した場合、液晶層10を介して参照線5と共通電極8との結合容量による共通電極電位の変動が観測される。この変動の対策としては、参照線5毎に駆動信号の符号を反転させた信号を利用する方法があり、さらに交流駆動信号の周期を走査時間毎にすることも可能である。

【0041】一方、交流信号をVcomとVrefの両方に入力し、駆動することも可能であり、駆動信号用ドライバICの低電圧化が可能となる。この駆動は、Vcomのみを交流駆動した場合と比較して、ドライバICの出力端子1個に流れる電流量あるいは、出力される電圧が低くなり、ドライバICが消費する電力を下げる事が可能となる。

【0042】各実施例におけるメモリ素子の活性層を構成する材料としては、単結晶シリコン、多結晶シリコン、アモルファスシリコンが考えられるが、特に本構造の表示素子は、3端子スイッチ素子の動作が可能な素子であれば、開閉時の抵抗値の比が 10^5 倍程度であることが望ましいが、最低で100倍程度であっても実施が可能と考える。これは、活性層を有機材料や150℃程度の低い温度、或いはそれ以下で成膜されたアモルファスシリコンなどの使用も考えられるようになり、各材料のプロセス上の制約、素子構造上の制約が緩和される。

【0043】また、フォトリソグラフィ工程を減らした素子などで、従来では表示素子として不十分なスイッチ特性の素子であっても、さらに高いコントラスト表示が得られる。また、図2(b)中の素子24を各種アニール等の方法で性能向上することでサイズの小型化を実現できる。一方、表示材料の液晶においても、電気光学的な材料特性が、通常使用範囲で経時劣化しないのであれば、フリッカが視認されにくい長周期側の交流信号（～10秒）に設定することも可能である。

【実施例4】メモリ素子のリフレッシュをする方法は、上述の通り表示画面に変化が発生しているラインに重み付けをすることで、他の静止画表示部分の消費電力を抑えることが実現できた。本駆動方法は、従来の線順次駆動（走査配線を順次走査する駆動法）の改良で駆動部分を構成できるが、認識された動画部分に対応した走査配線をスキャンすることが必要となる。動画部分を正確に認識し、動画部のみの信号情報を書き換えることは、単純に走査配線数を減少させる効果から低消費電力化となるが、駆動ICの構成が複雑となり、かえって消費電力の上昇を招くことになる。

【0044】そこで、動画表示部の指定ライン数をブロック化することで、トータルの駆動ICの消費電力の低減がはかれる。ブロック化するライン数としては、10～200、望ましくは50～100の走査線数がよい。ブロック化したラインの指定方法は、画像信号の入力部に画像メモリを設け動画部分を検出し、検出した走査ライン部のブロック位置と信号を駆動ICへ出力する。この出力をもとに、動画表示部分に対応したメモリ素子への信号供給を行う。

【0045】外部に画像メモリを有することは、該当するメモリの消費電力が本表示素子の消費電力に比べ低減されなければならない。理想では、表示面素毎に画像メモリを持つ必要があるが、例えば同一走査ラインの表示信号を一定周期或いは順次全てサンプリングして、2値情報をカウントした後、記憶してある前カウントデータとの比較を行うことで、簡易に動画を検出することができる。

【0046】この方法では、表示面素子がオン状態の総数が同じであった場合には、動画表示であっても認識することができないが、上述の方法に加えて、ブロック化した走査ライン部のメモリデータの合計を使用しての比較により、動画認識の誤差は大幅に減少可能となる。一方、本カウンタ方式で問題となるのは、サンプリング部とカウンタ部で発生するカウントミスである。カウントミスが多い場合には、全てを動画と認識してしまうために本構成回路の効果が期待できない。そこで、比較時に予めカウント誤差を考慮することで、本問題を解決できる。

【0047】画像メモリと同メモリ情報から動画の情報を得る動画検出部の構成を簡略化する方法としては、表示装置に半固定的な表示の重み付けをする方法も考えられる。具体的には、パソコン等のソフトウェアの多くは、表示画面の周辺部に選択用或いは機能表示の画面を有することが多い。この選択用の画面表示の多くは、変化することが多くない。このような場合、代表的なソフトウェアに対しては、予め動画表示が多くない領域が分かっているため、その領域に対する走査信号のリフレッシュの重み付けを下げる事が可能となる。

【0048】個別のソフトウェアに関しても、静止画である確率が高い表示領域が存在する場合には、ユーザがその領域を指定することで重み付けすることも可能となる。PDA等の操作画面がある程度予測可能な機器に関しては、表示装置側に画面のリフレッシュする重み付けを予め幾つか用意しておき、DIP-SW等のスイッチで指定する方法も可能である。

【0049】また、測定機器等の操作画面等においても、頻繁に画面の表示状態が変化する領域は、測定結果を表示する部分や操作案内をするメニューの部分が主となる。加えて、これら計測器などは、ユーザが操作パネルを操作しない場合は、測定結果の表示のみが変化する

ことが予め分かっているため、測定結果表示の部分に対応した画面を走査してメモリ素子への信号供給を行えばよいことになる。

【0050】この場合も、表示装置側での設定で対応できる。さらに細かくは、動画表示で走査されるライン数が少なければ、本装置の効果が高くなるので、動画表示部分が特定の連続した走査ライン上に集中するように、動画表示の画面をレイアウトすればよい。

(実施例5) 図9は本発明の第5の実施例に係わるアクティブマトリクス型液晶表示装置の1ブロックの概略回路構成図である。

【0051】ここでは、4ビット16階調表示の場合である。表示装置全体の画素ブロック数を $M \times N$ 個としたときの i, j 番目のブロック(i は $1 \sim M$ 、 j は $1 \sim N$)について示している。パソコンで現在主流のVGA規格の表示の場合、 $M=640$ 、 $N=480$ となる。

【0052】画面X方向のアドレス線 $ADRS-X_i$ と画面Y方向のアドレス線 $ADRS-Y_i$ との交点にANDゲート G_{ij} が設けられ、その出力と4本の画像データ線 $D_0 \sim D_3$ の各々の交点にANDゲート $G_{0ij} \sim G_{3ij}$ が設けられている。ANDゲート $G_{0ij} \sim G_{3ij}$ の出力はメモリ素子 $M_{0ij} \sim M_{3ij}$ に接続され、メモリ素子 $M_{0ij} \sim M_{3ij}$ の出力はスイッチングトランジスタ $T_{0ij} \sim T_{3ij}$ のゲート電極に接続され、スイッチングトランジスタ $T_{0ij} \sim T_{3ij}$ のオンオフを制御する。スイッチングトランジスタ $T_{0ij} \sim T_{3ij}$ のソース又はドレイン電極の一方は第1の共通電位線 COM_1 に、他方は画素電極を介して画素の液晶 $P_{0ij} \sim P_{3ij}$ に接続されている。

【0053】なお、本実施例のメモリ素子は第1の実施例で用いたようなスタティック型に限らず、ダイナミック型でもよいし、さらにEEPROMでもよく、各種の方式を利用することができる。

【0054】画素電極の面積はそれぞれ異なり、図10に示すように、 P_0 に対応した画素電極の面積を1とすると P_1 は2倍、 P_2 は4倍、 P_3 は8倍になっている。画素の液晶 $P_{0ij} \sim P_{3ij}$ の他端は共通電極である第2の共通電位線 COM_2 に接続されている。第1の共通電位線 COM_1 と第2の共通電位線 COM_2 の間には交流の液晶駆動電源 DRV が接続されている。

【0055】本実施例の動作は次のようになる。4ビットの画像データは、画面X方向のアドレス線 $ADRS-X_i$ と画面Y方向のアドレス線 $ADRS-Y_j$ が共にアクティブの時メモリ素子 $M_{0ij} \sim M_{3ij}$ に記憶され、次に再び選択されるまでその状態を保持し続ける。対向電極には、用いた液晶の駆動に必要な一定の交流電圧(例えば現在一般に使われているTN液晶では $\pm 5V$ の10V振幅の電圧)が印加されるが、この1画素毎に設けられたメモリ回路 $M_{0ij} \sim M_{3ij}$ によって制限されるスイッチングトランジスタ $T_{0ij} \sim T_{3ij}$ によって、画素の

液晶 $P_{0ij} \sim P_{3ij}$ には上記駆動電圧が印加されるか印加されないかが制御され、所望の表示状態が維持される。

【0056】従来のアクティブマトリクス液晶表示装置では、データ線駆動回路や制御回路の内部等価容量やデータ線配線容量負荷の充放電、対向電極容量の高速充放電のなどに大部分の電力が消費されていたが、本実施例では、従来のように表示画像が変化しなくても交流駆動のためにデータ線に一定周期の極性反転された信号を印加する必要がなく、データ線駆動回路や制御回路はほぼ停止状態のため、そこで消費される電力は殆ど無視できるほど小さくなる。唯一消費される電力は対向電極の直流駆動によるものとなるが、これはフリッカが視認されない程度の例えば60Hz以下の低い周波数で十分なため、消費電力は従来駆動法の100分の1から1000分の1程度に低減される。

【0057】この理由を、以下に説明する。対向電極全体の容量 C_{com} は、電極面積 S と液晶の誘電率 ϵ 、ギャップ d でほぼ決定され、 $C_{com} = \epsilon S / d$ となり、10インチクラスの液晶表示装置の場合その容量は0.1~0.3 μF 程度である。この容量を周波数 f_{drv} 、電圧 V_{drv} の交流電圧で充放電させるに消費される電力 P_{com} は、 $P_{com} = C_{com} \cdot f_{drv} \cdot V_{drv}^2$ で与えられ、 $\pm 5V$ で60Hzで駆動した場合には0.15mW~0.45mWと非常に小さいものになる。実際には、液晶のリーク抵抗やメモリ回路や駆動回路内のリーク電流による電力消費がそれに加算されるが、全体としての消費電力はそれでも1mWから数10mW程度に小さく抑えられる。

【0058】さらに、画素電極が所定数毎にブロック化され、そのブロック内の画素電極の寸法がそれぞれ異なっていることにより、1ブロックとして面積変調によるデジタル多階調表示が容易となる。従来の駆動法でこのような面積変調表示をしようとしたときの以下の問題が発生せず、極めて高画質の表示品位が得られる。

【0059】従来駆動では、TFTなどのスイッチ素子を持つ寄生容量によってスイッチング時に、表示性能に悪影響を及ぼす画素電位のレベルシフトが発生するが、このレベルシフト量は上記寄生容量と画素電極容量とのスイッチングノイズ電荷の分配比で決定され、画素電極の寸法が異なるとレベルシフト量は画素電極毎に異なり対向電極電位の調整によっても無害化することが困難であり、実質的に面積階調は不可能であった。

【0060】本実施例では、このスイッチングノイズ電荷によるレベルシフトは、液晶のリーク抵抗を通じてスイッチング終了後の初期に消滅するため、表示性能に悪影響を及ぼすことがなく、面積変調によるデジタル多階調表示が可能である。また、この方法では液晶の1画素の表示状態ではオン又はオフの2状態であるため、中間調表示時でも視野角は広く、表示むらやフリッカもな

い極めて良好な表示品位が得られる。

【0061】なお、本発明は上述した各実施例に限定されるものではない。実施例では、表示材料層として液晶を用いたが、これに限らず他の材料を用いることができる。例えば、ELやプラズマディスプレイ等に適用することが可能である。また、液晶の場合は、反射型に限らず透過型に適用することも可能である。その他、本発明の要旨を逸脱しない範囲で、種々変形して実施することができる。

【0062】

【発明の効果】以上詳述したように本発明によれば、1画素毎にスイッチ素子を制御するためのスタティック型のメモリ素子を設けているので、走査信号や画像信号を周期的に書き加える必要がなくなり、ドライバICで消費される電力を低減することができる。従って、従来型の電源装置の小型化、或いは充電型電源装置の使用時間延長を可能とする。

【0063】また本発明によれば、所定数の画素毎にブロック化して階調表示を行う方式において、1画素毎にスイッチ素子を制御するためのメモリ素子を設けているので、スイッチングノイズ電荷によるレベルシフトを抑制することができ、ドライバICの消費電力を低減することができ、かつ面積変調によるデジタル階調表示を行うことが可能となる。

【図面の簡単な説明】

【図1】第1の実施例に係わるアクティブマトリックス型液晶表示装置の基本構成を示す素子構造断面図と回路構成図。

【図2】第1の実施例の1画素部構成を示す回路構成図。

【図3】第1の実施例の変形例を示す回路構成図。

【図4】第1の実施例の変形例を示す回路構成図。

【図5】第1の実施例における駆動信号の一例を示す図。

【図6】第1の実施例における駆動信号の他の例を示す図。

【図7】第2の実施例に係わるアクティブマトリックス型液晶表示装置の1画素部構成を示す回路図とメモリ素子の構造断面図。

【図8】第2の実施例における駆動信号の一例を示す図。

【図9】第5の実施例に係わるアクティブマトリックス型液晶表示装置の1ブロックの概略回路構成図。

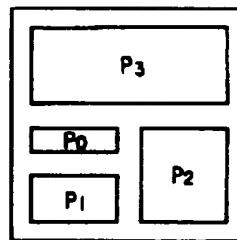
【図10】1ブロックにおける画素の大きさ及び配置例を示す図。

【図11】従来のアクティブマトリックス型液晶表示装置を示す回路構成図。

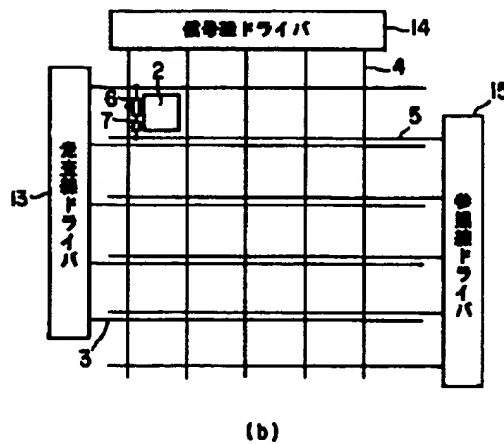
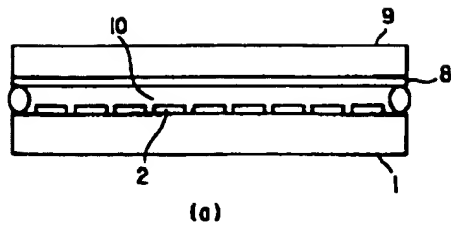
【符号の説明】

- 1…第1の基板
- 2…画素電極
- 3…走査線
- 4…信号線
- 5…参照線
- 6…メモリ素子
- 7…スイッチ素子
- 8…対向電極
- 9…第2のガラス基板
- 10…液晶層（表示材料層）
- 21…スイッチ素子
- 22, 23…インバータ素子
- 24…スイッチ素子

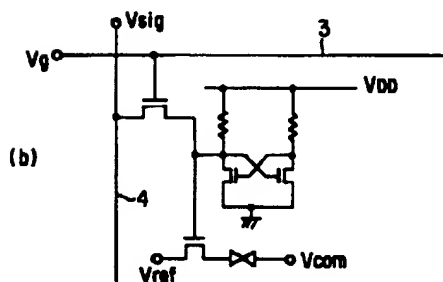
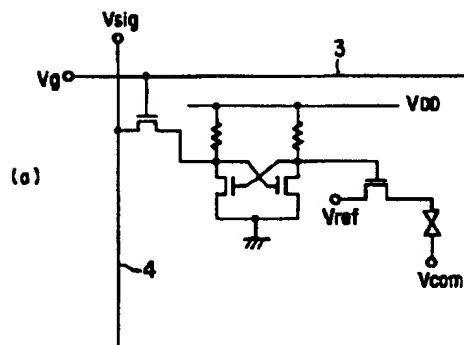
【図10】



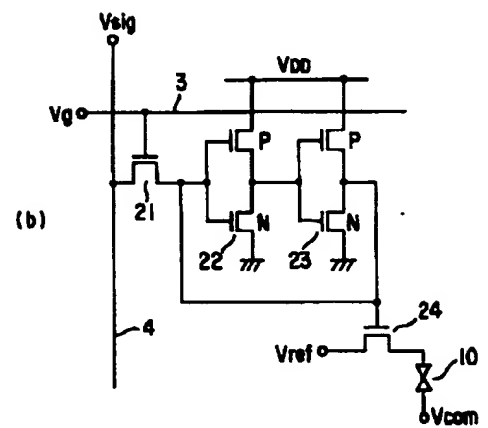
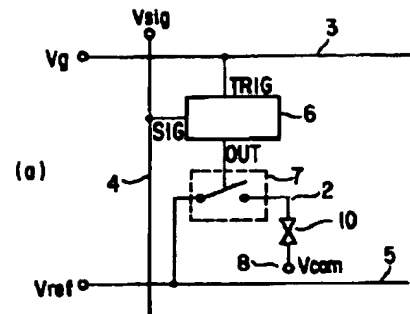
【図1】



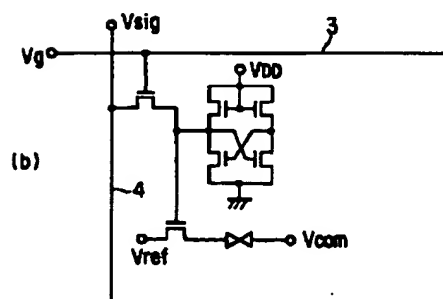
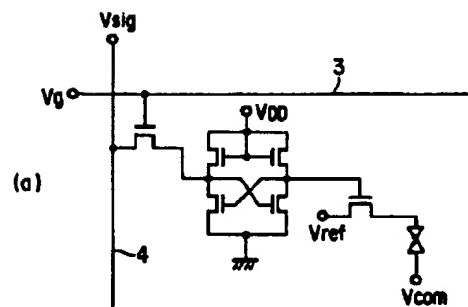
【図3】



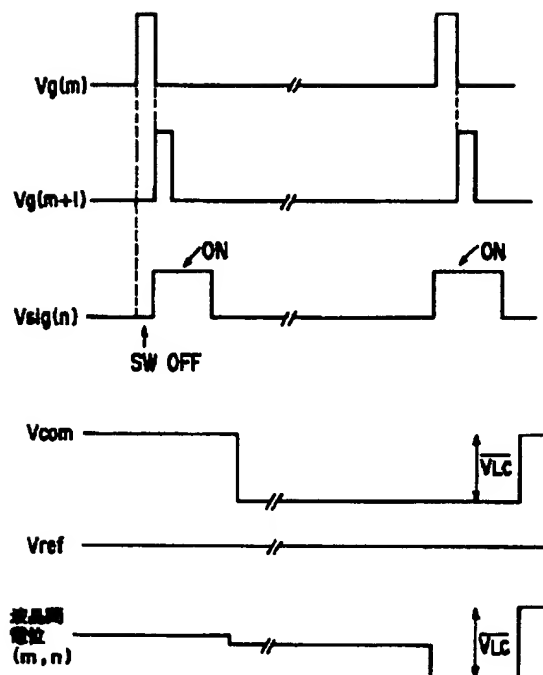
【図2】



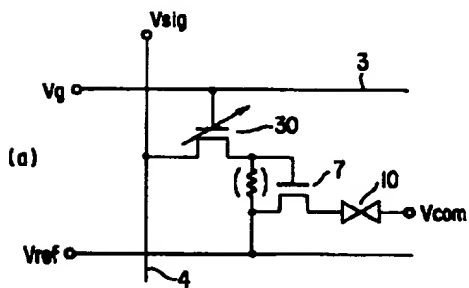
【図4】



【図5】

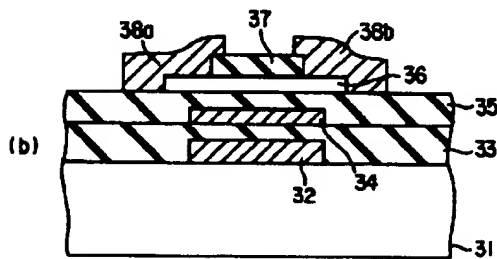


【図7】

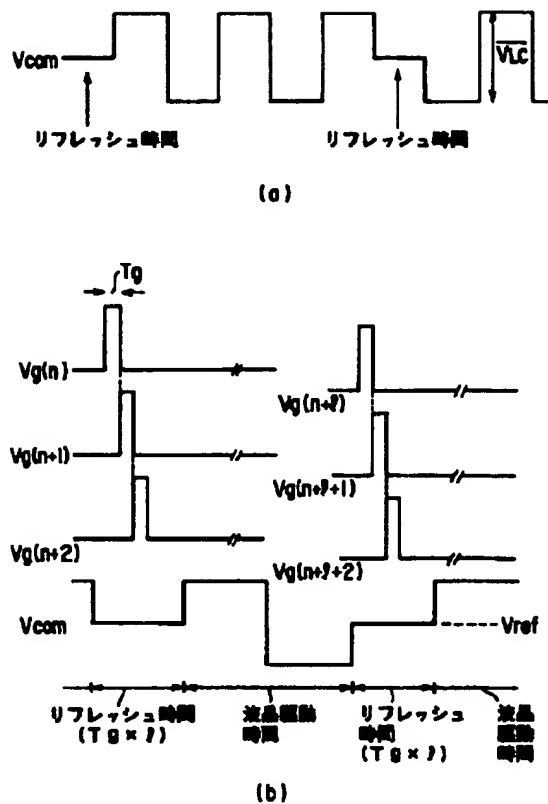


(a)

(b)

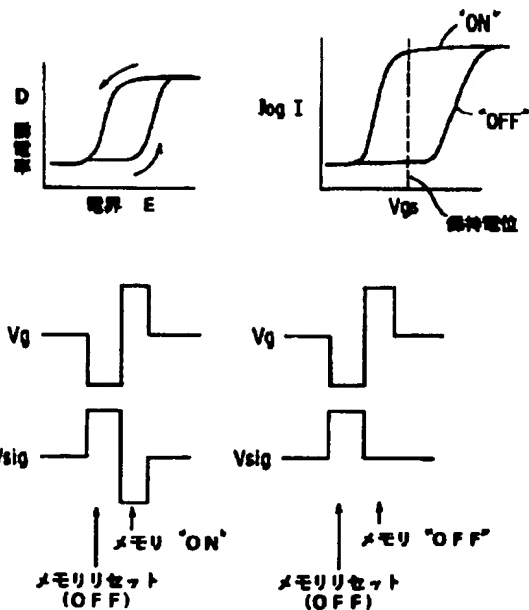


【図6】

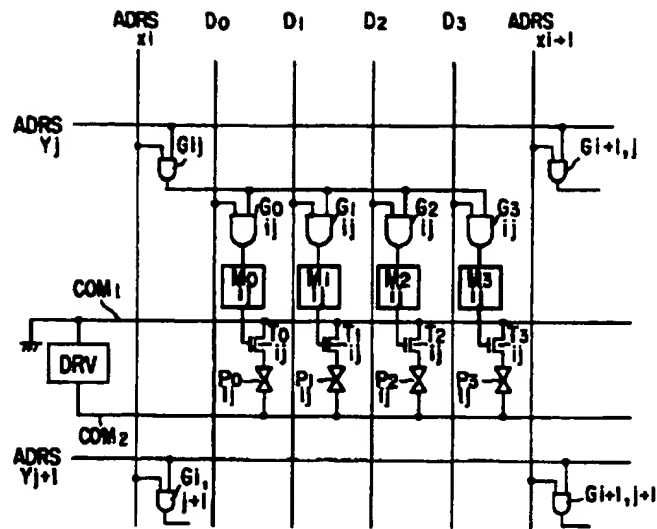


(b)

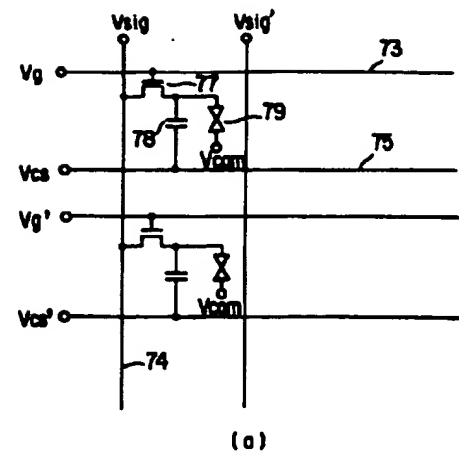
【図8】



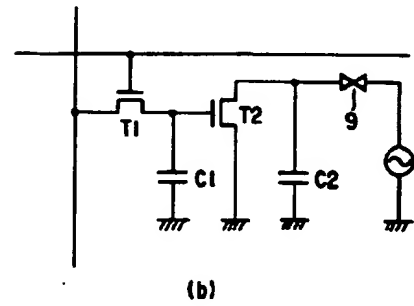
【図9】



【図11】



(a)



(b)

PATENT ABSTRACTS OF JAPAN

(11)Publication number : 08-194205
 (43)Date of publication of application : 30.07.1996

(51)Int. Cl. G02F 1/133
 G02F 1/1343
 G09B 3/36

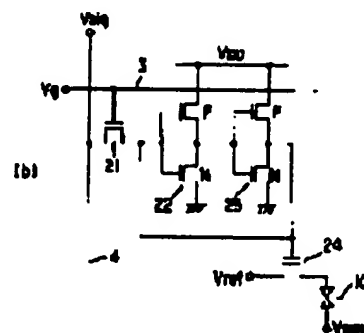
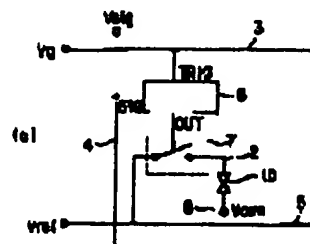
(21)Application number : 07-005742 (71)Applicant : TOSHIBA CORP
 (22)Date of filing : 18.01.1995 (72)Inventor : MOTAI TOMONOBU
 SUZUKI KOHEI

(54) ACTIVE MATRIX TYPE DISPLAY DEVICE

(57)Abstract:

PURPOSE: To provide an active matrix type liquid crystal display device with which the reduction of the electric power consumption of a driver IC is possible.

CONSTITUTION: This active matrix type liquid crystal display device has pixel electrodes 2 which are arranged in a matrix form on a first substrate, scanning lines 3 which are arranged in the horizontal direction between these pixel electrodes 2, signal lines 4 which are arranged in the vertical direction between the pixel electrodes 2, memory elements 6 of a static type which are respectively arranged in the respective intersected parts of the scanning lines 3 and the signal lines 4 and hold the binary display signals from the signal lines 4 according to the scanning signals from the scanning lines 3, switching elements 7 which are connected at one-side terminals to the pixel electrodes 2 and at their other-side terminals to wirings 5 applying reference potential and are turned on and off by the signals held in these memory elements 6, a second substrate which is arranged to face the first substrate and is provided with counter electrodes 8 so as to face the pixel electrodes 2 and a liquid crystal layer 10 which is disposed between the first and second substrates.



LEGAL STATUS

[Date of request for examination] 19.12.2001
 [Date of sending the examiner's decision of rejection]
 [Kind of final disposal of application]

other than the examiner's decision of
rejection or application converted
registration]
[Date of final disposal for application]
[Patent number]
[Date of registration]
[Number of appeal against examiner's
decision of rejection]
[Date of requesting appeal against
examiner's decision of rejection]
[Date of extinction of right]

Copyright (C); 1998, 2000 Japan Patent Office

*** NOTICES ***

Japan Patent Office is not responsible for any damages caused by the use of this translation.

1. This document has been translated by computer. So the translation may not reflect the original precisely.
2. **** shows the word which can not be translated.
3. In the drawings, any words are not translated.

CLAIMS

[Claim]

[Claim 1] The pixel electrode arranged in the shape of a matrix on the 1st substrate, and two or more scanning lines arranged along with ** on the other hand on the 1st substrate, Two or more signal lines arranged in the orientation which crosses with the aforementioned scanning line on the 1st substrate, The static type memory device holding the binary status signal inputted from the aforementioned signal line according to the scanning signal which has been arranged, respectively and was inputted into each intersection of the aforementioned scanning line and the aforementioned signal line from the aforementioned scanning line, The switching device which turns between terminals on and off with the signal which it was prepared corresponding to these memory devices, respectively, and one terminal was connected to the aforementioned pixel electrode, was connected to the wiring whose other-end child gives a reference potential, and was held at the aforementioned memory device, Active matrix type display which opposite arrangement is carried out with the 1st substrate, and is characterized by coming to provide the display material layer prepared between the 2nd substrate in which the counterelectrode was prepared so that it might counter with the aforementioned pixel electrode, and the 1st and 2nd substrates.

[Claim 2] The aforementioned display material layer is the active matrix type display of the claim 1 publication characterized by impressing an alternating current signal to either [at least] the wiring which is liquid crystal and gives the aforementioned reference potential, or a counterelectrode.

[Claim 3] The pixel electrode arranged in the shape of a matrix on a substrate, and two or more scanning lines arranged along with ** on the other hand on the aforementioned substrate, Two or more signal lines arranged in the orientation which crosses with the aforementioned scanning line on the aforementioned substrate, The memory device holding the status signal inputted from the aforementioned signal line according to the scanning signal which has been arranged at each intersection of the aforementioned scanning line and the aforementioned signal line, and was inputted from the aforementioned scanning line, Corresponding to these memory devices, it is prepared, respectively, and one terminal is connected to the aforementioned pixel electrode. It comes to provide the switching device from which the resistance between terminals changes with the signals which were connected to the wiring whose other-end child gives a reference potential, and were held at the aforementioned memory device. Active matrix type display characterized by blocking the aforementioned pixel electrode for every predetermined number, and the dimensions of the pixel electrode within this block differing, respectively.

[Translation done.]

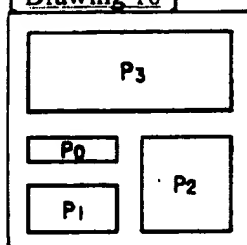
* NOTICES *

Japan Patent Office is not responsible for any damages caused by the use of this translation.

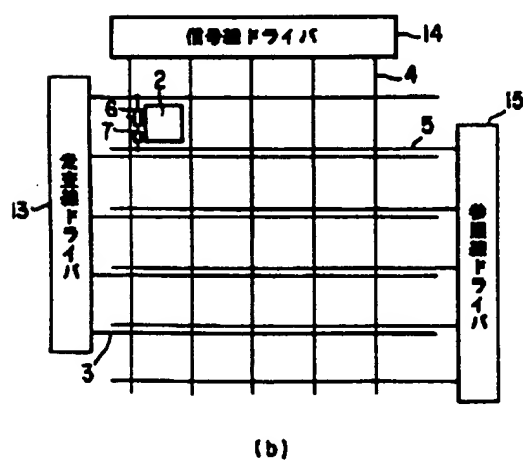
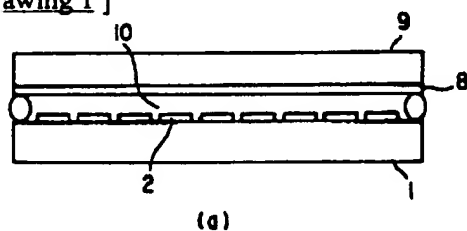
1. This document has been translated by computer. So the translation may not reflect the original precisely.
2. **** shows the word which can not be translated.
3. In the drawings, any words are not translated.

DRAWINGS

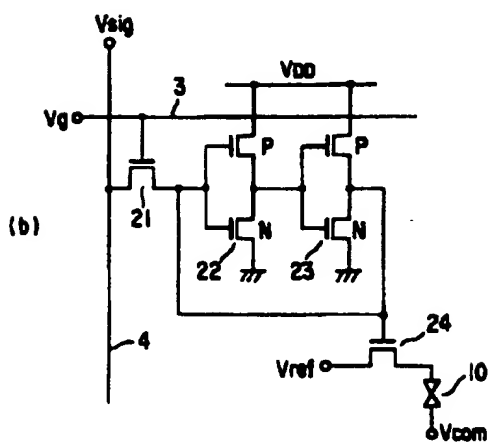
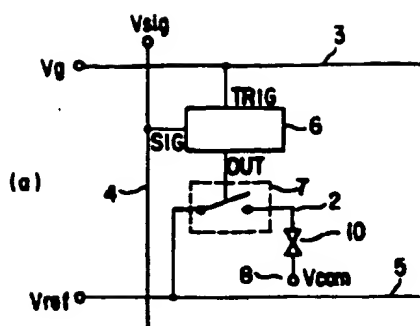
[Drawing 10]



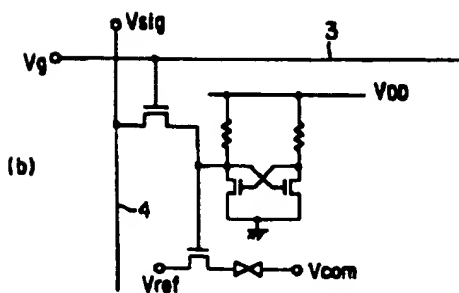
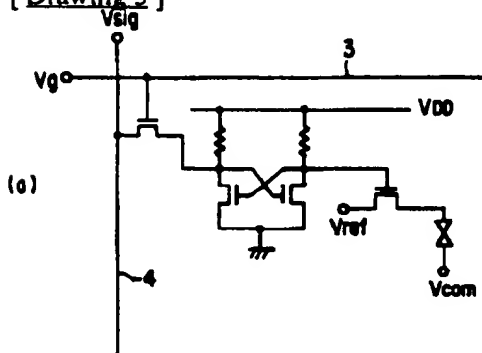
[Drawing 1]



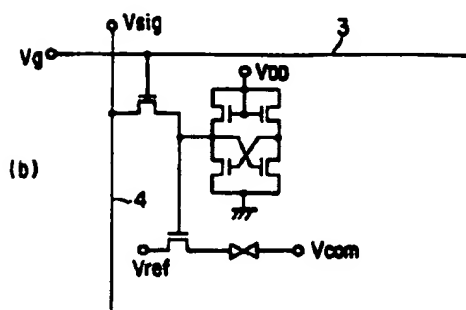
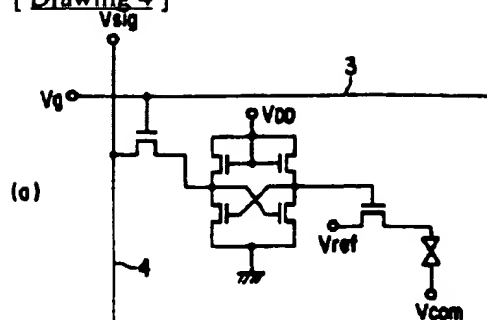
[Drawing 2]



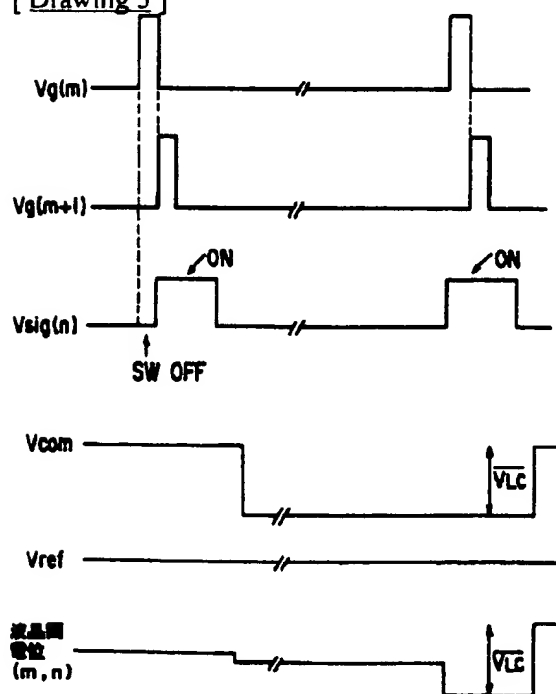
[Drawing 3]



[Drawing 4]

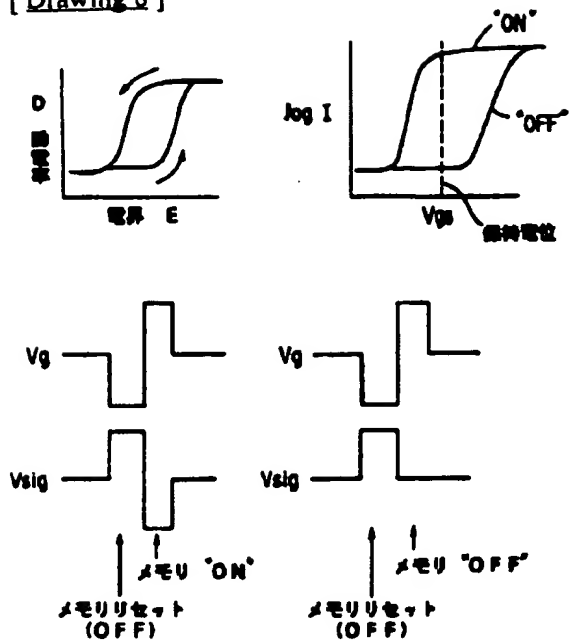


[Drawing 5]

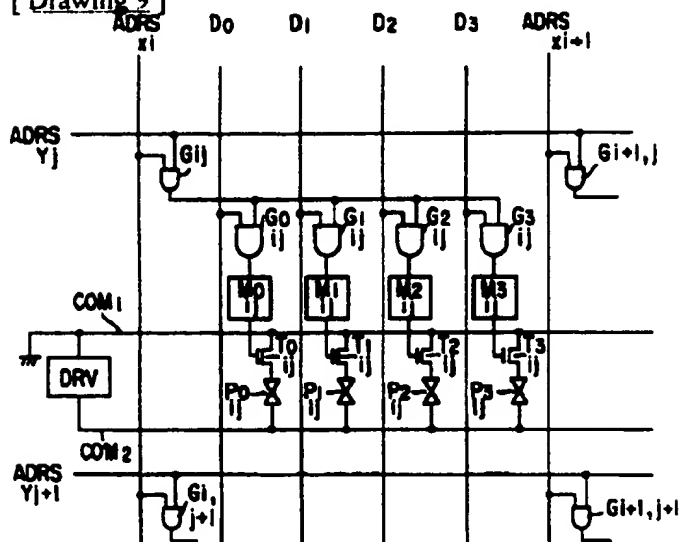


[Drawing 6]

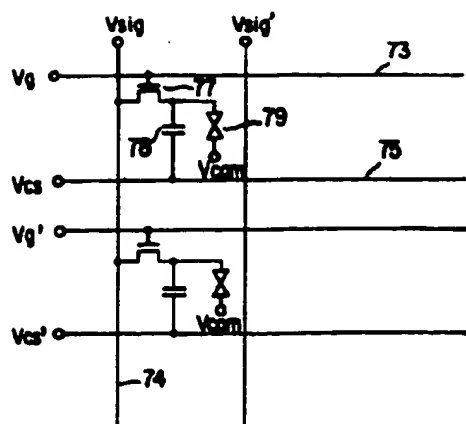
[Drawing 8]



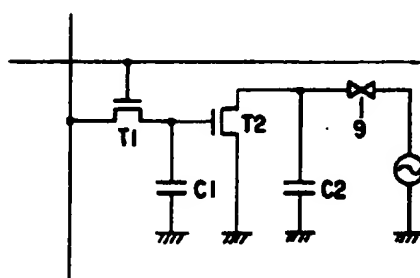
[Drawing 9]



[Drawing 11]



(a)



(b)

[Translation done.]

*** NOTICES ***

Japan Patent Office is not responsible for any damages caused by the use of this translation.

1. This document has been translated by computer. So the translation may not reflect the original precisely.
2. **** shows the word which can not be translated.
3. In the drawings, any words are not translated.

DETAILED DESCRIPTION

[Detailed description]

[0001]

[Field of the Invention] Especially this invention relates to the active matrix type display using switching devices, such as TFT, with respect to image display equipments, such as a liquid crystal display.

[0002]

[Prior art] In recent years, the development of the display of thin shapes, such as a liquid crystal display, is performed actively. Especially the demand to a display of portable [which can be carried anywhere], or a big screen is increasing, and it is asked for long-time-izing of lightweight-izing and a time, and low-power-ization. For that, the effect by the technique of lowering the power consumption of the display [itself] other than highly-efficient-izing of the dc-battery for power is large.

[0003] At a LCD, the luminous efficacy of the inverter for the fluorescence spool used as a backlighting, a light guide plate, and fluorescence spools is low, and since the effect by efficient-izing to the power with which the present condition is consumed with these lightings is large, there is almost no attempt of the power consumption reduction by enhancement of a display material or the display panel [itself]. However, it is thought required to reduce the power consumption of the display panel [itself] in the future.

[0004] It is thought that the power consumption of the display panel [itself] is mainly dependent on the drive technique of a driver-IC property and a display panel, and enhancement of low-battery-izing of a use driver IC is advanced. However, it is not easy to reduce the power consumption of a transistor which takes charge of each pixel drive of a driver IC by the technique (TFT-LCD) of preparing switching devices, such as TFT (TFT), in the display pixel section, and repeating a picture signal a short period and writing it in.

[0005] By TFT-LCD of a present 10 inch class, although a back light lighting is about [5W] about [1.5W], in order for the power consumption of a circuit system to long-time-ize a cell operation, as for own power consumption of a display panel, less than [1W] and less than [desirable / 0.2W] in which a drive by the small lightweight cell is possible are demanded. The problem of this power consumption becomes remarkable from the penetrated type display accompanied by a lighting with the reflected type display accompanied by a lighting. In the display of 50cm or more of the vertical angles especially used for the display for an advertisement etc., consumed electric power was producing the constraint of an installation.

[0006] Drawing 11 (a) is the circuit-arrangement view showing the conventional active matrix type LCD. TFT 77, a pixel section electrode, etc. of the scanning line 73, the signal line 74, the common wiring 75, and 3 terminal switching device are created by the thin film process, and a scanning signal and a picture signal are respectively inputted into the scanning line 73 and the signal line 74 from a driver IC according to it. Here, TFT 77 into which the scanning signal was inputted will be in an ON state, and it is transmitted to liquid crystal 79 while the picture signal from a signal line 74 is accumulated at the supplementary capacity 78. When a scanning signal is not inputted, since TFT 77

will be in an OFF state, the picture signal impressed at the time of ON is held as it is at liquid crystal 79.

[0007] It obtains with the signals to write in, and even if it is the same picture image, when [required] carrying out the alternating current drive of the liquid crystal material, it will be necessary to make TFT into an ON state by the scanning signal, and to re-write in a picture signal again, in such a LCD of structure. Therefore, since the driver IC for - picture signals for scanning signals which generates a driving signal operates continuously, power is always consumed.

[0008] On the other hand, as shown in drawing 11 (b), the method of operating the 2nd switching device T2 is proposed by holding an analog signal to a capacitive load C1 by the 1st switching device T1 (J. Vanfleteren (IDRC1988, p 74-79)). However, in order not to make the ***** data further held since the capacity load C2 connected with the switching device T2 and this became large as the size of a display pixel becomes large produce change, the switching device T1 with the capacity to drive the mass load capacity C1 is needed.

[0009] For example, elevation of the on resistance of T2 occurs by the threshold voltage whose capacity value of C1 on a design is a level decrement of the ON signal sent to T2 when T1 becomes off [from ON] to a parvus case, and the boundary voltage from which T2 will be in an ON state too much carrying out change with the passage of time, and the target display is not attained. In addition, large-sized-ization of C1 etc. will cause elevation of power consumption. The problem on these designs is because this element configuration consists of an analog-sample hold circuit, and it was asked for the display of a new configuration.

[0010] On the other hand, in the active matrix type LCD, the method of performing the digital gradation display by the area modulation is proposed. This changes the dimension of each pixel electrode within a block, and carries out adjustable [of the display pixel area of each block] in digital by choosing the pixel which should be displayed within each block while it blocks a pixel electrode for every predetermined number.

[0011] However, by the conventional drive technique, the level shift of the pixel potential which affects a display performance at the time of switching occurs by the parasitic capacitance which switching devices, such as TFT, have. It is difficult to determine this amount of level shifts by the partition ratio of the switching noise charge of a parasitic capacitance and pixel electrode capacitance, for the amounts of level shifts to differ for every pixel electrode, when the dimensions of a pixel electrode differ, and to make it harmless also by adjustment of counterelectrode potential. Therefore, area gradation was substantially impossible.

[0012]

[Object of the Invention] Thus, although the method of driving it using an analog-sample hold circuit for a reduction of the power consumption of a driver IC rather than carrying out the direct drive of the switching device for supplying a signal to display material layers, such as liquid crystal, by the scanning line was proposed conventionally, effect sufficient by this technique has not been attained.

[0013] Moreover, area gradation was substantially [difficult / it / for the level shift of the pixel potential by the switching noise charge to occur, for these amounts of level shifts to differ for every pixel electrode in the example which performs the digital gradation display by the area modulation, when the dimensions of a pixel electrode differ, and to make it harmless also by adjustment of counterelectrode potential / therefore] impossible.

[0014] this invention was made in consideration of the above-mentioned situation, and the place made into the purpose is to offer the active matrix type display which can reduce the power consumption of a driver IC.

[0015] Moreover, it is in other purposes of this invention offering the active matrix type display which could reduce the power consumption of a driver IC and enabled the digital gradation display by the area modulation.

[0016]

[The means for solving a technical problem] In order to solve the above-mentioned technical problem, this invention has adopted the following configurations. Namely, this invention (claim 1) is set to the

active matrix type display which prepared the switching device in each pixel by which matrix arrangement was carried out. The pixel electrode arranged in the shape of a matrix on the 1st substrate, and two or more scanning lines arranged along with ** on the other hand on the 1st substrate, Two or more signal lines arranged in the orientation which crosses with the aforementioned scanning line on the 1st substrate, The static type memory device holding the binary status signal inputted from a signal line according to the scanning signal which has been arranged, respectively and was inputted into each intersection of the aforementioned scanning line and the aforementioned signal line from the scanning line, The switching device which turns between terminals on and off with the signal which it was prepared corresponding to these memory devices, respectively, and one terminal was connected to the aforementioned pixel electrode, was connected to the wiring whose other-end child gives a reference potential, and was held at the aforementioned memory device, Opposite arrangement is carried out with the 1st substrate, and it is characterized by coming to provide the display material layer prepared between the 2nd substrate in which the counterelectrode was prepared so that it might counter with the aforementioned pixel electrode, and the 1st and 2nd substrates.

[0017] Here, the following are raised as a desirable embodiment of this invention.

- (1) A display material layer should be liquid crystal.
- (2) The scanning line and the signal line should be arranged pixel inter-electrode.
- (3) Impress an alternating current signal to either [at least] the wiring which gives a reference potential, or a counterelectrode.
- (4) When scanning selection of the memory device connected to the same scanning line is carried out, let the alternating current signal impressed from a wiring or a counterelectrode be fixed potential.
- (5) The memory device holding a binary status signal should be formed of non-volatile memory.
- (6) The memory device and the switching device should be formed of TFT.

[0018] Moreover, this invention (claim 4) is set to the active matrix type display which prepared the switching device in each pixel by which matrix arrangement was carried out. The pixel electrode arranged in the shape of a matrix on a substrate, and two or more scanning lines arranged along with ** on the other hand on the aforementioned substrate, Two or more signal lines arranged in the orientation which crosses with the aforementioned scanning line on the aforementioned substrate, The memory device holding the status signal inputted from a signal line according to the scanning signal which has been arranged at each intersection of the aforementioned scanning line and the aforementioned signal line, and was inputted from the scanning line, Corresponding to these memory devices, it is prepared, respectively, and one terminal is connected to the aforementioned pixel electrode. It connects with the wiring whose other-end child gives a reference potential, and it comes to provide the switching device from which the resistance between terminals changes with the signals held at the aforementioned memory device, the aforementioned pixel electrode is blocked for every predetermined number, and it is characterized by the dimensions of the pixel electrode within this block differing, respectively.

- (1) A display material layer should be liquid crystal.
- (2) The scanning line and the signal line should be arranged pixel inter-electrode.
- (3) A switching device should operate in the two status of turning on and off, and should be equipped with the drive circuit which drives two or more signal lines and scanning lines with the potential of two status, respectively.
- (4) The memory device, the switching device, and the drive circuit should consist of the TFT formed on the same substrate.
- (5) Use a memory device as an image memory of an application system.

[0019]

[Operation] It is not necessary to rewrite periodically until the information which should be displayed by the pixel changes to a degree, and according to this invention (claim 1), the status is maintained by the static type memory device prepared for every pixel. When the display information on a display pixel does not change, since rewriting of the information on a memory device is unnecessary, the power which becomes unnecessary to add a scanning signal and a picture signal periodically, and is consumed by the driver IC is reduced.

[0020] That is, although a great portion of power was conventionally consumed by the charge and discharge of a capacity load with equipment, even if a display image does not change like before in this invention, it is not necessary to impress the signal which the fixed period inverted to a signal line for an alternating current drive, and most power with which the drive circuit which drives a signal line is mostly consumed there for a idle state becomes so small that it can ignore. Although the power by which an only consumption is carried out becomes what is depended on an alternating current drive of a counterelectrode, this is the grade by which a flicker is not ****ed, for example, since the low frequency of 60Hz or less is enough, power consumption is conventionally reduced drastically [about 1/1000] from 1/100 of the driving method.

[0021] Moreover, since the static type is used as a memory device, the big switching device with the capacity to drive a mass load capacity and this is not needed, and it is effective in the reduction of power consumption also from this point. Furthermore, although it was difficult to extend the signal rewriting period to a pixel from the off property of a switching device, or a constraint of flicker **** in the former in the case of the LCD, it is enabled to extend the rewriting period of all display pixels, and 1-pixel rewriting time with the equipment of this invention.

[0022] Moreover, according to this invention (claim 4), a pixel electrode is blocked for every predetermined number, and when the dimensions of the pixel electrode within the block differ, respectively, the digital multi-gradation display by the area modulation becomes easy as 1 block. Although the level shift of the pixel potential by the switching noise charge occurred as mentioned above when it was going to carry out an area modulation display in this way by the conventional driving method, in this invention, the level shift by this switching noise charge disappears the first stage after a switching end through the leakage resistance of photoelectrical transducer material, such as liquid crystal. For this reason, a display performance is not affected and the digital multi-gradation display by the area modulation is possible.

[0023] Furthermore, since the 1-pixel display status of photoelectrical transducer material, such as liquid crystal, is in ON or two off status, also in the time of a halftone display, an angle of visibility is large and the very good display quality which display unevenness does not have, either is obtained.

[0024]

[Example] The LCD which created the example of this invention hereafter using the TFT formed at the thin film process adapting well-known semiconductor technique is explained as an example.

(Example 1) Drawing 1 shows the basic configuration of the active matrix type LCD concerning the 1st example of this invention, (a) is an element structure-section view and (b) is a circuit-arrangement view. The pixel electrode 2 is arranged in the shape of a matrix on the 1st substrate 1 which consists of glass etc., between the pixel electrodes 2, the scanning line 3 is arranged at a space longitudinal direction, and the signal line 4 is arranged in the vertical orientation. Moreover, the reference line 5 is arranged in parallel with the scanning line 3. The memory device 6 later mentioned to the intersection of the scanning line 3 and the signal line 4 is formed, and the switching device 7 is formed between the memory device 6 and the pixel electrode 2.

[0025] Opposite arrangement of the 2nd substrate 9 which carries out predetermined ***** on a substrate 1, and consists of glass etc. is carried out, and the counterelectrode 8 is formed in the opposite side of a substrate 9. And the liquid crystal layer 10 as a display material layer is enclosed between each substrate 1 and 9. In addition, as for a scanning-line driver and 14, 13 in drawing is [a signal-line driver and 15] reference-line drivers.

[0026] Drawing 2 (a) is the circuit diagram showing the 1 pixel section configuration of this example. The binary data-hold memory device 6 is connected to the intersection of the scanning line 3 formed in the shape of a matrix, and the signal line 4, and the output section which outputs the information currently held is prepared in this memory device 6. The control terminal of 3 terminal switching device 7 is connected to the output section. This switching device 7 controls the resistance between a reference line 5 and the pixel electrode 2, and is adjusting the bias status of the liquid crystal layer 10.

[0027] It can consider, the memory circuit, i.e., the static type memory device, of the type which carried out positive feedback, using a two step inverter as an example of the memory device in drawing 2 (a).

This circuit is not enough as the off property of a transistor, and it has in it the characteristic feature whose implementation is possible as an element for analog signals with the transistor element which cannot be used.

[0028] Concrete circuit arrangement are shown in drawing 2 (b). Since capacity C1 is unnecessary, the element 21 of drawing 2 corresponding to the element T1 of drawing 11 (b) as compared with aforementioned drawing 11 (b) may be small. Each element size of a switching device 21 and the inverter-circuit sections 22 and 23 can be designed by the same view as optimum number-of-stages ratio n of the inverter-circuit section. Specifically, when the ratio of the element size of elements 21, 22, 23, and 24 specifies by $1:n:n:n$, $n=1-100$ and ***** $n=2-10$ are good design conditions.

[0029] The example of circuit arrangement of the 1 pixel section which used other memory devices for drawing 3 (a), (b), and drawing 4 (a) and (b) is shown. Drawing 3 (a), (b), and drawing 4 (a) and (b) show the example of a configuration from which the connection position of 3 terminal switching device is different, respectively. Since the element number which a display pixel constitutes from structure conventionally increases, although optical use luminous efficacy decreases in a penetrated type display device, since a memory device etc. can be formed in the bottom of a reflector, a fall of the optical use luminous efficacy by this display device is not produced by the reflected type LCD.

[0030] A drive wave serves as a line sequential drive like a drive of the conventional LCD like drawing 5. A sequential-scanning pulse is impressed to the scanning line 3, and the signal which controls opening and closing of a switching device 7 is inputted into the memory device 6 synchronized with this through a signal line 4. On the other hand, an alternating current signal is inputted into a common electrode (counterelectrode 8). If the conditions of the ratio of the resistance of a liquid crystal material and the resistance of a switching device are satisfied as above-mentioned, a good display will be attained by above-mentioned circuit and drive.

[0031] If change of this equipment is lost to a display image like a static image on an ideal, the refreshment to a memory device 6 is unnecessary. However, like drawing 5, by the drive by the simple square-wave input, since the liquid crystal potential by the side of a switch is fixed by one of the potential status of the high potential of an alternating current driving signal, or low potential when a switch changes from an ON state to an OFF state, a direct-current-voltage component will be applied to the liquid crystal section. Therefore, in order to improve a display performance, it will be necessary to prepare the refreshment term for a liquid crystal potential setup in case a switch changes to an OFF state.

[0032] As easiest technique, there is a method of preparing a blanking term between the alternating current signals of a common electrode like drawing 6 (a). In the device of a conventional type, since parallel connection of the capacity 78 which guarantees the potential fall by the liquid crystal 79 of drawing 11 (a) or the leakage current of a switching device 77 was carried out to liquid crystal capacity, it was not easy to shorten the write-in time of a signal. Like drawing 2 (b), it accepts and comes out, and for a certain reason, the time of refreshment is shorter than the scan time which is spent for the signal for gate opening and closing of a switching device 21 and which is looked at by the element of a conventional type, and can be managed with the element of this invention.

[0033] Moreover, like drawing 6 (b), not all pixels are refreshed continuously but it is also possible to divide the time of the line to refresh and to insert between the liquid crystal driving signals which are rectangle signals. Although it is desirable that the memory on [all] a line is refreshed as for the inserting method when it sees in fixed time, it is also possible to attach and refresh weight on the display line which is the fixed position of a scan line, and corresponds when the display screen changes (for example, when the amount of blink display is a fixed position).

[0034] In addition, in drawing 6 (b), T_g is refreshment pulse width, l is 1 time of the number of refreshment lines, and the number of times of refreshment for 1 screen rewriting is defined by the $(\text{number of gate lines}) / l$.

[0035] Thus, since according to this example the static type memory device 6 is formed for every pixel and it is made to drive a switching device 7 for the storage information on this element 6, when a display information does not change, rewriting of the information on a memory device 7 is unnecessary. For this

reason, the power which becomes unnecessary to add a scanning signal and a picture signal periodically, and is consumed by the driver IC is reduced sharply.

[0036] Moreover, since a memory device 6 is a static type, the big switching device T1 which has the capacity to drive the mass load capacity C1 and this, like before shown in aforementioned drawing 11 (b) is not needed, and it is effective in the reduction of power consumption also from this point.

Furthermore, in this example, the off property of a switching device or a constraint of flicker **** is suppressed, and it is enabled to extend the rewriting period and the 1-pixel rewriting time which are all display pixels.

[0037] the status that the power consumption trial calculation by TFT-LCD of the 10 inch class which used the amorphous silicon thin film does not rewrite the display screen in this example -- 10mW and per second -- a stroke -- large low-power-ization of 1/50 was [less than 30mW and the former / as rewriting status of a field] realizable

(Example 2) Drawing 7 is for explaining the active matrix type LCD concerning the 2nd example of this invention, and the circuit diagram in which (a) shows a 1 pixel section configuration, and (b) are the structure-section views of a memory device.

[0038] Fundamentally, although this example is the same as that of the 1st example, as shown in drawing 7 (a), non-volatile memory rewritable as a memory device 30 is used for it. The concrete configuration of a memory device 30 is as being shown in drawing 7 (b), and makes the gate of usual reverse stagger type TFT two-layer structure. 31 in drawing -- a substrate and 32 -- for the 2nd gate (floating gate) and 35, a tunnel insulator layer and 36 are [the 1st gate (control gate) and 33 / a gate insulator layer and 34 / a protection insulator layer, and 38a and 38b of barrier layers, such as a-Si, and 37] source drain electrodes

[0039] The number of times of rewriting is 107 which is the standard of the number of times of switching of a drive conventionally. Although it is an ideal to satisfy the rewriting operation more than a time, if it is the display with which a still picture display serves as a subject, the number of times of rewriting can decrease 100 - 1/10000, and can be used as a memory device of this display. Although the above-mentioned memory device serves as EEPROM configuration, it can constitute the display with it. [same when the electric-field-dielectric constant curve (D-E curve) of dielectric materials consists of a material which has a property in a hysteresis]

[0040] Specifically, as shown in drawing 8, a memory device is created by using the dielectric materials which have a hysteresis as a gate insulator layer, it is controlling the voltage between terminals applied to a memory device, and a reset of a memory device and the signal writing of memory are performed. As shown in drawing, in addition to the technique of connecting TFT 7 to a memory device, connection of a memory device is also possible by enhancement of a driving signal to the direct presentation electrode.

(Example 3) Although an alternating current signal is inputted only into Vcom (common electrode 8) and the liquid crystal material is driven in the 1st example, you may input an alternating current signal into Vref side (reference line 5). When an alternating current signal is inputted into Vref, change of the common electrode potential by the joint capacity of a reference line 5 and the common electrode 8 is observed through the liquid crystal layer 10. It is also possible for there to be a method of using the signal which reversed the sign of a driving signal every reference line 5, and to carry out the period of an alternating current driving signal for every scan time further as a cure of this change.

[0041] On the other hand, it is Vcom about an alternating current signal. Vref It inputs into both, and driving is also possible and low-battery-ization of the driver IC for driving signals of it is attained. This drive is Vcom. As compared with the case where an alternating current drive is carried out, the amount of currents which flows to one output terminal of a driver IC, or the voltage outputted becomes low, and it is enabled to lower the power which a driver IC consumes.

[0042] As a material which constitutes the barrier layer of the memory device in each example, although single crystal silicon, polycrystal silicon, and an amorphous silicon can be considered, if especially the display device of this structure is an element which can operate 3 terminal switching device, the ratio of the resistance at the time of opening and closing is 105. Although it is desirable that it is about [twice],

even if it is about 100 times at the lowest, it is thought that enforcement is possible. Use of the amorphous silicon by which this was ***** less than [an organic material, the low temperature of about 150 degrees C, or it] in the barrier layer also comes to be considered, and the constraint on the process of each material and the constraint on element structure are eased.

[0043] Moreover, with the element which reduced the phot ***** fee process, even if it is the element of the switch property with the former inadequate as a display device, a still high contrast display is obtained. Moreover, a miniaturization of a size is realizable by carrying out enhancement of the element 24 in drawing 2 (b) in a performance by technique, such as various annealing. It is also possible to set it as the alternating current signal by the side of the long period by which a flicker is seldom ***** (- 10 seconds) on the other hand, if an electro-optics-material property does not usually carry out a degradation with the passage of time in the use domain in the liquid crystal of a display material.

(Example 4) The technique refreshed for a memory device is making a weighting the line which change has generated in the display screen as above-mentioned, and it has realized stopping other power consumption for a still picture display. Although this drive technique can constitute a part for a mechanical component from enhancement of the conventional line sequential drive (the driving method which scans a scanning wiring sequentially), it is necessary to carry out the scan of the scanning wiring corresponding to the recognized animation fraction. Although it becomes low-power-ization to recognize an animation fraction correctly and to rewrite the signaling information of only the animation section from the effect of decreasing the number of scanning wirings simply, constituting of drive IC becomes complicated and elevation of power consumption will be caused on the contrary.

[0044] Then, a reduction of the power consumption of total drive IC can be aimed at by blocking the number of specification lines of the animation display section. the number of lines to block ***** -- 10-200 -- the number of scanning lines of 50-100 is desirably good The specification technique of the blocked line prepares an image memory in the input section of a picture signal, and outputs the block position and signal of the scan line section which detected and detected the animation fraction to drive IC. On the basis of this output, signal supply to the memory device corresponding to the animation display fraction is performed.

[0045] The power consumption of the memory to which having an image memory outside corresponds must be reduced compared with the power consumption of this display device. In an ideal, although it is necessary to have an image memory for every display pixel, an animation is simply detectable by performing the comparison with the pre-count data which have memorized the status signal of the same scan line, for example a fixed period or after sampling all one by one and counting a binary information.

[0046] Although it cannot recognize by this technique even if it is animation display when the total whose display pixel is an ON state is the same, in addition to above-mentioned technique, the decrement of the error of an animation recognition is sharply attained by the comparison which uses the sum of the blocked memory data of the scan line section. On the other hand, the count mistake generated in the thump ***** section and the counter section poses a problem by this counter formula. When there are many count mistakes, in order to recognize all to be an animation, the effect of this configuration circuit cannot be expected. Then, this problem is solvable by taking a count error into consideration beforehand at the time of a comparison.

[0047] How to make the weighting of a semipermanent display display as simplification technique is also considered in the configuration of the animation detecting element which acquires the information on an animation from an image memory and this memory information. Specifically, many of software of a personal computer etc. has the screen of the object for selection, or a functional display in many cases among the circumference section of the display screen. Many of screen display for this selection does not change in many cases. In such a case, since the field which does not have much animation display is beforehand known to typical software, it is enabled to lower the weighting of the refreshment of a scanning signal to the field.

[0048] When the viewing area with the high probability which is a still picture exists also about

individual software, it also becomes possible to carry out a weighting by an user specifying the field. The technique of operation screens, such as PDA, preparing for the display side beforehand the weighting for which a screen is refreshed partly about the device which can to some extent be predicted, and specifying with switches, such as DIP-SW, is also possible.

[0049] Moreover, also in operation screens, such as a measuring equipment, etc., the field where the display status of a screen changes frequently becomes main [the fraction of the menu which carries out the fraction which displays a measurement result, and operation guidance]. In addition, since these measuring instruments etc. understand beforehand that only a display of a measurement result changes when an user does not operate a control panel, they will scan the screen corresponding to the fraction of a measurement result display, and should just perform signal supply to a memory device.

[0050] Also in this case, it can correspond by setup by the side of display. What is necessary is just to arrange the screen of animation display so that an animation display fraction may concentrate on the scan line which specialization followed since the effect of this equipment will become high, if there are few lines scanned by animation display still finely.

(Example 5) Drawing 9 is the 1-block outline circuit-arrangement view of the active matrix type LCD concerning the 5th example of this invention.

[0051] Here, it is in the case of a 4 bit 16 gradation display. The block (i1-M, j1-N) of ij position when making the pixel block count of the whole display into MxN piece is shown. In a display of mainstream VGA specification, it is set to M= 640 and N= 480 with a personal computer now.

[0052] The AND gate Gij is formed in the intersection of address-line ADRS-Xi of the orientation of screen X, and address-line ADRS-Yj of the orientation of screen Y, and AND-gate G0ij - G3 ij are formed in each intersection of the output and four image data lines D0-D3. The output of AND-gate G0ij - G3 ij is connected to memory device M0ij-M3ij, it connects with the gate electrode of switching-transistor T0ij-T3ij, and the output of memory device M0ij-M3ij controls turning on and off of switching-transistor T0ij-T3ij. Another side is connected to 1st common potential line COM1 through the pixel electrode at liquid crystal P0ij-P3ij of a pixel for either the source of switching-transistor T0ij-T3ij, or the drain electrode.

[0053] In addition, not only a static type but a dynamic type which was used in the 1st example is sufficient as the memory device of this example, EEPROM is further sufficient as it and it can use various kinds of formulae.

[0054] If area of the pixel electrode corresponding to P0 is set to 1 as the area of a pixel electrode differs, respectively and is shown in drawing 10, twice and P2 have increased 4 times and P3 has increased [P1] 8 times. The other end of liquid crystal P0ij-P3ij of a pixel is connected to 2nd common potential line COM2 which is a common electrode. Between 1st common potential line COM1 and 2nd common potential line COM2, the liquid crystal drive power DRV of an alternating current is connected.

[0055] An operation of this example is as follows. Both 4-bit image data continues holding the status until address-line ADRS-Yj of address-line ADRS-Xi of the orientation of screen X and the orientation of screen Y is memorized by active time memory device M0ij-M3ij and is next chosen again. Although fixed alternating voltage (for example, TN liquid crystal currently used for general present **5 voltage of 10V amplitude of V) required for a drive of the used liquid crystal is impressed to a counterelectrode It is controlled [by which the above-mentioned driver voltage is impressed to liquid crystal P0ij-P3ij of a pixel / or or] by switching-transistor T0ij-T3ij restricted by this memory circuit M0ij-M3ij prepared for every pixel whether impression is carried out, and the desired display status is maintained.

[0056] Although a great portion of power was consumed by the charge and discharge of the internal equivalent capacity of a data-line drive circuit or a control circuit, or a data-line wiring capacity load, the high-speed charge and discharge of counterelectrode capacity, etc. in the conventional active matrix LCD Even if a display image does not change like before, it is not necessary to impress the signal which the fixed period inverted to the data line for an alternating current drive, and in this example, most power with which a data-line drive circuit and a control circuit are mostly consumed there for a idle state becomes so small that it can ignore. Although the power by which an only consumption is carried out

becomes what is depended on a direct-current drive of a counterelectrode, this is the grade by which a flicker is not ****ed, for example, since the low frequency of 60Hz or less is enough, power consumption is conventionally reduced by 1/100 to about 1/1000 of the driving method.

[0057] This ground is explained below. Capacity C_{com} of the whole counterelectrode It determines mostly by dielectric constant [of electrode area S and liquid crystal] ϵ , and gap d , and is set to $C_{com} = \epsilon S / d$, and, in the case of the LCD of a 10 inch class, the capacity is about 0.1-0.3 micro F. They are frequency f_{drv} and voltage V_{drv} about this capacity. Power P_{com} consumed by carrying out charge and discharge by alternating voltage $P_{com} = C_{com} \cdot f_{drv} \cdot V_{drv}^2$ It is given, and when it drives by 60Hz $\cdot 5V$, it is set very much to 0.15mW - 0.45mW to a parvus thing. In fact, although the power consumption by the leakage current in the leakage resistance and memory circuit of liquid crystal, or a drive circuit is added to it, the power consumption as whole is still stopped small about several 10mW from 1mW.

[0058] Furthermore, a pixel electrode is blocked for every predetermined number, and when the dimensions of the pixel electrode within the block differ, respectively, the digital multi-gradation display by the area modulation becomes easy as 1 block. The following problems when carrying out such an area modulation display by the conventional driving method do not occur, but very high-definition display quality is obtained.

[0059] Although the level shift of the pixel potential which affects a display performance at the time of switching occurred by the drive conventionally by the parasitic capacitance which switching devices, such as TFT, have, when this amount of level shifts is determined by the partition ratio of the switching noise charge of the above-mentioned parasitic capacitance and pixel electrode capacitance and the dimensions of a pixel electrode differed, the amount of level shifts was difficult to differ for every pixel electrode and to make it harmless also by adjustment of counterelectrode potential, and area gradation was substantially impossible.

[0060] In this example, since the level shift by this switching noise charge disappears the first stage after a switching end through the leakage resistance of liquid crystal, it does not affect a display performance and the digital multi-gradation display by the area modulation is possible for it. Moreover, by this technique, since it is in ON or two off status in the state of a 1-pixel display of liquid crystal, also in the time of a halftone display, an angle of visibility is large and the very good display quality which neither display unevenness nor a flicker also has is obtained.

[0061] In addition, this invention is not limited to each example mentioned above. In the example, although liquid crystal was used as a display material layer, not only this but other materials can be used. For example, applying to EL, a plasma display, etc. is possible. Moreover, in the case of liquid crystal, it is possible not only a reflected type but to apply to a penetrated type. In addition, in the domain which does not deviate from the summary of this invention, it can deform variously and can carry out.

[0062]

[Effect of the invention] Since the memory device of the static type for controlling a switching device for every pixel is provided according to this invention as explained in full detail above, the power which becomes unnecessary to add a scanning signal and a picture signal periodically, and is consumed by the driver IC can be reduced. Therefore, miniaturization of the power unit of a conventional type or time extension of a charged type power unit is enabled.

[0063] Moreover, since the memory device for controlling a switching device for every pixel is prepared in the formula which blocks for every pixel of a predetermined number and performs a gradation display according to this invention, it is enabled to be able to suppress the level shift by the switching noise charge, and to be able to reduce the power consumption of a driver IC, and to perform the digital gradation display by the area modulation.

[Translation done.]

*** NOTICES ***

Japan Patent Office is not responsible for any damages caused by the use of this translation.

1. This document has been translated by computer. So the translation may not reflect the original precisely.
2. **** shows the word which can not be translated.
3. In the drawings, any words are not translated.

TECHNICAL FIELD

[Field of the Invention] Especially this invention relates to the active matrix type display using switching devices, such as TFT, with respect to image display equipments, such as a liquid crystal display.

[Translation done.]

*** NOTICES ***

Japan Patent Office is not responsible for any damages caused by the use of this translation.

1. This document has been translated by computer. So the translation may not reflect the original precisely.
2. **** shows the word which can not be translated.
3. In the drawings, any words are not translated.

PRIOR ART

[Prior art] In recent years, the development of the display of thin shapes, such as a liquid crystal display, is performed actively. Especially the demand to a display of portable [which can be carried anywhere], or a big screen is increasing, and it is asked for long-time-izing of lightweight-izing and a time, and low-power-ization. For that, the effect by the technique of lowering the power consumption of the display [itself] other than highly-efficient-izing of the dc-battery for power is large.

[0003] At a LCD, the luminous efficacy of the inverter for the fluorescence spool used as a backlighting, a light guide plate, and fluorescence spools is low, and since the effect by efficient-izing to the power with which the present condition is consumed with these lightings is large, there is almost no attempt of the power consumption reduction by enhancement of a display material or the display panel [itself]. However, it is thought required to reduce the power consumption of the display panel [itself] in the future.

[0004] It is thought that the power consumption of the display panel [itself] is mainly dependent on the drive technique of a driver-IC property and a display panel, and enhancement of low-battery-izing of a use driver IC is advanced. However, it is not easy to reduce the power consumption of a transistor which takes charge of each pixel drive of a driver IC by the technique (TFT-LCD) of preparing switching devices, such as TFT (TFT), in the display pixel section, and repeating a picture signal a short period and writing it in.

[0005] By TFT-LCD of a present 10 inch class, although a back light lighting is about [5W] about [1.5W], in order for the power consumption of a circuit system to long-time-ize a cell operation, as for own power consumption of a display panel, less than [1W] and less than [desirable / 0.2W] in which a drive by the small lightweight cell is possible are demanded. The problem of this power consumption becomes remarkable from the penetrated type display accompanied by a lighting with the reflected type display accompanied by a lighting. In the display of 50cm or more of the vertical angles especially used for the display for an advertisement etc., consumed electric power was producing the constraint of an installation.

[0006] Drawing 11 (a) is the circuit-arrangement view showing the conventional active matrix type LCD. TFT 77, a pixel section electrode, etc. of the scanning line 73, the signal line 74, the common wiring 75, and 3 terminal switching device are created by the thin film process, and a scanning signal and a picture signal are respectively inputted into the scanning line 73 and the signal line 74 from a driver IC according to it. Here, TFT 77 into which the scanning signal was inputted will be in an ON state, and it is transmitted to liquid crystal 79 while the picture signal from a signal line 74 is accumulated at the supplementary capacity 78. When a scanning signal is not inputted, since TFT 77 will be in an OFF state, the picture signal impressed at the time of ON is held as it is at liquid crystal 79.

[0007] It obtains with the signals to write in, and even if it is the same picture image, when [required] carrying out the alternating current drive of the liquid crystal material, it will be necessary to make TFT into an ON state by the scanning signal, and to re-write in a picture signal again, in such a LCD of structure. Therefore, since the driver IC for - picture signals for scanning signals which generates a

driving signal operates continuously, power is always consumed.

[0008] On the other hand, as shown in drawing 11 (b), the method of operating the 2nd switching device T2 is proposed by holding an analog signal to a capacitive load C1 by the 1st switching device T1 (J. Vanfleteren (IDRC1988, p 74-79)). However, in order not to make the ***** data further held since the capacity load C2 connected with the switching device T2 and this became large as the size of a display pixel becomes large produce change, the switching device T1 with the capacity to drive the mass load capacity C1 is needed.

[0009] For example, elevation of the on resistance of T2 occurs by the threshold voltage whose capacity value of C1 on a design is a level decrement of the ON signal sent to T2 when T1 becomes off [from ON] to a parvus case, and the boundary voltage from which T2 will be in an ON state too much carrying out change with the passage of time, and the target display is not attained. In addition, large-sized-ization of C1 etc. will cause elevation of power consumption. The problem on these designs is because this element configuration consists of an analog-sample hold circuit, and it was asked for the display of a new configuration.

[0010] On the other hand, in the active matrix type LCD, the method of performing the digital gradation display by the area modulation is proposed. This changes the dimension of each pixel electrode within a block, and carries out adjustable [of the display pixel area of each block] in digital by choosing the pixel which should be displayed within each block while it blocks a pixel electrode for every predetermined number.

[0011] However, by the conventional drive technique, the level shift of the pixel potential which affects a display performance at the time of switching occurs by the parasitic capacitance which switching devices, such as TFT, have. It is difficult to determine this amount of level shifts by the partition ratio of the switching noise charge of a parasitic capacitance and pixel electrode capacitance, for the amounts of level shifts to differ for every pixel electrode, when the dimensions of a pixel electrode differ, and to make it harmless also by adjustment of counterelectrode potential. Therefore, area gradation was substantially impossible.

[Translation done.]

*** NOTICES ***

Japan Patent Office is not responsible for any damages caused by the use of this translation.

1. This document has been translated by computer. So the translation may not reflect the original precisely.
2. **** shows the word which can not be translated.
3. In the drawings, any words are not translated.

EFFECT OF THE INVENTION

[Effect of the invention] Since the memory device of the static type for controlling a switching device for every pixel is provided according to this invention as explained in full detail above, the power which becomes unnecessary to add a scanning signal and a picture signal periodically, and is consumed by the driver IC can be reduced. Therefore, miniaturization of the power unit of a conventional type or time extension of a charged type power unit is enabled.

[0063] Moreover, since the memory device for controlling a switching device for every pixel is prepared in the formula which blocks for every pixel of a predetermined number and performs a gradation display according to this invention, it is enabled to be able to suppress the level shift by the switching noise charge, and to be able to reduce the power consumption of a driver IC, and to perform the digital gradation display by the area modulation.

[Translation done.]

*** NOTICES ***

Japan Patent Office is not responsible for any damages caused by the use of this translation.

1. This document has been translated by computer. So the translation may not reflect the original precisely.
2. **** shows the word which can not be translated.
3. In the drawings, any words are not translated.

TECHNICAL PROBLEM

[Object of the Invention] Thus, although the method of driving it using an analog-sample hold circuit for a reduction of the power consumption of a driver IC rather than carrying out the direct drive of the switching device for supplying a signal to display material layers, such as liquid crystal, by the scanning line was proposed conventionally, effect sufficient by this technique has not been attained.

[0013] Moreover, area gradation was substantially [difficult / it / for the level shift of the pixel potential by the switching noise charge to occur, for these amounts of level shifts to differ for every pixel electrode in the example which performs the digital gradation display by the area modulation, when the dimensions of a pixel electrode differ, and to make it harmless also by adjustment of counterelectrode potential / therefore] impossible.

[0014] this invention was made in consideration of the above-mentioned situation, and the place made into the purpose is to offer the active matrix type display which can reduce the power consumption of a driver IC.

[0015] Moreover, it is in other purposes of this invention offering the active matrix type display which could reduce the power consumption of a driver IC and enabled the digital gradation display by the area modulation.

[Translation done.]

*** NOTICES ***

Japan Patent Office is not responsible for any damages caused by the use of this translation.

1. This document has been translated by computer. So the translation may not reflect the original precisely.
2. **** shows the word which can not be translated.
3. In the drawings, any words are not translated.

MEANS

[The means for solving a technical problem] In order to solve the above-mentioned technical problem, this invention has adopted the following configurations. Namely, this invention (claim 1) is set to the active matrix type display which prepared the switching device in each pixel by which matrix arrangement was carried out. The pixel electrode arranged in the shape of a matrix on the 1st substrate, and two or more scanning lines arranged along with ** on the other hand on the 1st substrate, Two or more signal lines arranged in the orientation which crosses with the aforementioned scanning line on the 1st substrate, The static type memory device holding the binary status signal inputted from a signal line according to the scanning signal which has been arranged, respectively and was inputted into each intersection of the aforementioned scanning line and the aforementioned signal line from the scanning line, The switching device which turns between terminals on and off with the signal which it was prepared corresponding to these memory devices, respectively, and one terminal was connected to the aforementioned pixel electrode, was connected to the wiring whose other-end child gives a reference potential, and was held at the aforementioned memory device, Opposite arrangement is carried out with the 1st substrate, and it is characterized by coming to provide the display material layer prepared between the 2nd substrate in which the counterelectrode was prepared so that it might counter with the aforementioned pixel electrode, and the 1st and 2nd substrates.

[0017] Here, the following are raised as a desirable embodiment of this invention.

- (1) A display material layer should be liquid crystal.
- (2) The scanning line and the signal line should be arranged pixel inter-electrode.
- (3) Impress an alternating current signal to either [at least] the wiring which gives a reference potential, or a counterelectrode.
- (4) When scanning selection of the memory device connected to the same scanning line is carried out, let the alternating current signal impressed from a wiring or a counterelectrode be fixed potential.
- (5) The memory device holding a binary status signal should be formed of non-volatile memory.
- (6) The memory device and the switching device should be formed of TFT.

[0018] Moreover, this invention (claim 4) is set to the active matrix type display which prepared the switching device in each pixel by which matrix arrangement was carried out. The pixel electrode arranged in the shape of a matrix on a substrate, and two or more scanning lines arranged along with ** on the other hand on the aforementioned substrate, Two or more signal lines arranged in the orientation which crosses with the aforementioned scanning line on the aforementioned substrate, The memory device holding the status signal inputted from a signal line according to the scanning signal which has been arranged at each intersection of the aforementioned scanning line and the aforementioned signal line, and was inputted from the scanning line, Corresponding to these memory devices, it is prepared, respectively, and one terminal is connected to the aforementioned pixel electrode. It connects with the wiring whose other-end child gives a reference potential, and it comes to provide the switching device from which the resistance between terminals changes with the signals held at the aforementioned memory device, the aforementioned pixel electrode is blocked for every predetermined number, and it is characterized by the dimensions of the pixel electrode within this block differing, respectively.

- (1) A display material layer should be liquid crystal.
- (2) The scanning line and the signal line should be arranged pixel inter-electrode.
- (3) A switching device should operate in the two status of turning on and off, and should be equipped with the drive circuit which drives two or more signal lines and scanning lines with the potential of two status, respectively.
- (4) The memory device, the switching device, and the drive circuit should consist of the TFT formed on the same substrate.
- (5) Use a memory device as an image memory of an application system.

[Translation done.]

*** NOTICES ***

Japan Patent Office is not responsible for any damages caused by the use of this translation.

1. This document has been translated by computer. So the translation may not reflect the original precisely.
2. **** shows the word which can not be translated.
3. In the drawings, any words are not translated.

OPERATION

[Operation] It is not necessary to rewrite periodically until the information which should be displayed by the pixel changes to a degree, and according to this invention (claim 1), the status is maintained by the static type memory device prepared for every pixel. When the display information on a display pixel does not change, since rewriting of the information on a memory device is unnecessary, the power which becomes unnecessary to add a scanning signal and a picture signal periodically, and is consumed by the driver IC is reduced.

[0020] That is, although a great portion of power was conventionally consumed by the charge and discharge of a capacity load with equipment, even if a display image does not change like before in this invention, it is not necessary to impress the signal which the fixed period inverted to a signal line for an alternating current drive, and most power with which the drive circuit which drives a signal line is mostly consumed there for a idle state becomes so small that it can ignore. Although the power by which an only consumption is carried out becomes what is depended on an alternating current drive of a counterelectrode, this is the grade by which a flicker is not ****ed, for example, since the low frequency of 60Hz or less is enough, power consumption is conventionally reduced drastically [about 1/1000] from 1/100 of the driving method.

[0021] Moreover, since the static type is used as a memory device, the big switching device with the capacity to drive a mass load capacity and this is not needed, and it is effective in the reduction of power consumption also from this point. Furthermore, although it was difficult to extend the signal rewriting period to a pixel from the off property of a switching device, or a constraint of flicker **** in the former in the case of the LCD, it is enabled to extend the rewriting period of all display pixels, and 1-pixel rewriting time with the equipment of this invention.

[0022] Moreover, according to this invention (claim 4), a pixel electrode is blocked for every predetermined number, and when the dimensions of the pixel electrode within the block differ, respectively, the digital multi-gradation display by the area modulation becomes easy as 1 block. Although the level shift of the pixel potential by the switching noise charge occurred as mentioned above when it was going to carry out an area modulation display in this way by the conventional driving method, in this invention, the level shift by this switching noise charge disappears the first stage after a switching end through the leakage resistance of photoelectrical transducer material, such as liquid crystal. For this reason, a display performance is not affected and the digital multi-gradation display by the area modulation is possible.

[0023] Furthermore, since the 1-pixel display status of photoelectrical transducer material, such as liquid crystal, is in ON or two off status, also in the time of a halftone display, an angle of visibility is large and the very good display quality which display unevenness does not have, either is obtained.

[Translation done.]

*** NOTICES ***

Japan Patent Office is not responsible for any damages caused by the use of this translation.

1. This document has been translated by computer. So the translation may not reflect the original precisely.
2. **** shows the word which can not be translated.
3. In the drawings, any words are not translated.

EXAMPLE

[Example] The LCD which created the example of this invention hereafter using the TFT formed at the thin film process adapting well-known semiconductor technique is explained as an example.

(Example 1) Drawing 1 shows the basic configuration of the active matrix type LCD concerning the 1st example of this invention, (a) is an element structure-section view and (b) is a circuit-arrangement view. The pixel electrode 2 is arranged in the shape of a matrix on the 1st substrate 1 which consists of glass etc., between the pixel electrodes 2, the scanning line 3 is arranged at a space longitudinal direction, and the signal line 4 is arranged in the vertical orientation. Moreover, the reference line 5 is arranged in parallel with the scanning line 3. The memory device 6 later mentioned to the intersection of the scanning line 3 and the signal line 4 is formed, and the switching device 7 is formed between the memory device 6 and the pixel electrode 2.

[0025] Opposite arrangement of the 2nd substrate 9 which carries out predetermined ***** on a substrate 1, and consists of glass etc. is carried out, and the counterelectrode 8 is formed in the opposite side of a substrate 9. And the liquid crystal layer 10 as a display material layer is enclosed between each substrate 1 and 9. In addition, as for a scanning-line driver and 14, 13 in drawing is [a signal-line driver and 15] reference-line drivers.

[0026] Drawing 2 (a) is the circuit diagram showing the 1 pixel section configuration of this example. The binary data-hold memory device 6 is connected to the intersection of the scanning line 3 formed in the shape of a matrix, and the signal line 4, and the output section which outputs the information currently held is prepared in this memory device 6. The control terminal of 3 terminal switching device 7 is connected to the output section. This switching device 7 controls the resistance between a reference line 5 and the pixel electrode 2, and is adjusting the bias status of the liquid crystal layer 10.

[0027] It can consider, the memory circuit, i.e., the static type memory device, of the type which carried out positive feedback, using a two step inverter as an example of the memory device in drawing 2 (a). This circuit is not enough as the off property of a transistor, and it has in it the characteristic feature whose implementation is possible as an element for analog signals with the transistor element which cannot be used.

[0028] Concrete circuit arrangement are shown in drawing 2 (b). Since capacity C1 is unnecessary, the element 21 of drawing 2 corresponding to the element T1 of drawing 11 (b) as compared with aforementioned drawing 11 (b) may be small. Each element size of a switching device 21 and the inverter-circuit sections 22 and 23 can be designed by the same view as optimum number-of-stages ratio n of the inverter-circuit section. Specifically, when the ratio of the element size of elements 21, 22, 23, and 24 specifies by $1:n:n:n$, $n=1-100$ and ***** $n=2-10$ are good design conditions.

[0029] The example of circuit arrangement of the 1 pixel section which used other memory devices for drawing 3 (a), (b), and drawing 4 (a) and (b) is shown. Drawing 3 (a), (b), and drawing 4 (a) and (b) show the example of a configuration from which the connection position of 3 terminal switching device is different, respectively. Since the element number which a display pixel constitutes from structure conventionally increases, although optical use luminous efficacy decreases in a penetrated type display device, since a memory device etc. can be formed in the bottom of a reflector, a fall of the optical use

luminous efficacy by this display device is not produced by the reflected type LCD.

[0030] A drive wave serves as a line sequential drive like a drive of the conventional LCD like drawing 5. A sequential-scanning pulse is impressed to the scanning line 3, and the signal which controls opening and closing of a switching device 7 is inputted into the memory device 6 synchronized with this through a signal line 4. On the other hand, an alternating current signal is inputted into a common electrode (counterelectrode 8). If the conditions of the ratio of the resistance of a liquid crystal material and the resistance of a switching device are satisfied as above-mentioned, a good display will be attained by above-mentioned circuit and drive.

[0031] If change of this equipment is lost to a display image like a static image on an ideal, the refreshment to a memory device 6 is unnecessary. However, like drawing 5, by the drive by the simple square-wave input, since the liquid crystal potential by the side of a switch is fixed by one of the potential status of the high potential of an alternating current driving signal, or low potential when a switch changes from an ON state to an OFF state, a direct-current-voltage component will be applied to the liquid crystal section. Therefore, in order to improve a display performance, it will be necessary to prepare the refreshment term for a liquid crystal potential setup in case a switch changes to an OFF state.

[0032] As easiest technique, there is a method of preparing a blanking term between the alternating current signals of a common electrode like drawing 6 (a). In the device of a conventional type, since parallel connection of the capacity 78 which guarantees the potential fall by the liquid crystal 79 of drawing 11 (a) or the leakage current of a switching device 77 was carried out to liquid crystal capacity, it was not easy to shorten the write-in time of a signal. Like drawing 2 (b), it accepts and comes out, and for a certain reason, the time of refreshment is shorter than the scan time which is spent for the signal for gate opening and closing of a switching device 21 and which is looked at by the element of a conventional type, and can be managed with the element of this invention.

[0033] Moreover, like drawing 6 (b), not all pixels are refreshed continuously but it is also possible to divide the time of the line to refresh and to insert between the liquid crystal driving signals which are rectangle signals. Although it is desirable that the memory on [all] a line is refreshed as for the inserting method when it sees in fixed time, it is also possible to attach and refresh weight on the display line which is the fixed position of a scan line, and corresponds when the display screen changes (for example, when the amount of blink display is a fixed position).

[0034] In addition, in drawing 6 (b), T_g is refreshment pulse width, l is 1 time of the number of refreshment lines, and the number of times of refreshment for 1 screen rewriting is defined by the (number of gate lines) / l .

[0035] Thus, since according to this example the static type memory device 6 is formed for every pixel and it is made to drive a switching device 7 for the storage information on this element 6, when a display information does not change, rewriting of the information on a memory device 7 is unnecessary. For this reason, the power which becomes unnecessary to add a scanning signal and a picture signal periodically, and is consumed by the driver IC is reduced sharply.

[0036] Moreover, since a memory device 6 is a static type, the big switching device T1 which has the capacity to drive the mass load capacity C1 and this, like before shown in aforementioned drawing 11 (b) is not needed, and it is effective in the reduction of power consumption also from this point. Furthermore, in this example, the off property of a switching device or a constraint of flicker **** is suppressed, and it is enabled to extend the rewriting period and the 1-pixel rewriting time which are all display pixels.

[0037] the status that the power consumption trial calculation by TFT-LCD of the 10 inch class which used the amorphous silicon thin film does not rewrite the display screen in this example -- 10mW and per second -- a stroke -- large low-power-ization of 1/50 was [less than 30mW and the former / as rewriting status of a field] realizable

(Example 2) Drawing 7 is for explaining the active matrix type LCD concerning the 2nd example of this invention, and the circuit diagram in which (a) shows a 1 pixel section configuration, and (b) are the structure-section views of a memory device.

[0038] Fundamentally, although this example is the same as that of the 1st example, as shown in drawing 7 (a), non-volatile memory rewritable as a memory device 30 is used for it. The concrete configuration of a memory device 30 is as being shown in drawing 7 (b), and makes the gate of usual reverse stagger type TFT two-layer structure. 31 in drawing -- a substrate and 32 -- for the 2nd gate (floating gate) and 35, a tunnel insulator layer and 36 are [the 1st gate (control gate) and 33 / a gate insulator layer and 34 / a protection insulator layer, and 38a and 38b of barrier layers, such as a-Si, and 37] source drain electrodes

[0039] The number of times of rewriting is 107 which is the standard of the number of times of switching of a drive conventionally. Although it is an ideal to satisfy the rewriting operation more than a time, if it is the display with which a still picture display serves as a subject, the number of times of rewriting can decrease 100 - 1/10000, and can be used as a memory device of this display. Although the above-mentioned memory device serves as EEPROM configuration, it can constitute the display with it. [same when the electric-field-dielectric constant curve (D-E curve) of dielectric materials consists of a material which has a property in a hysteresis]

[0040] Specifically, as shown in drawing 8, a memory device is created by using the dielectric materials which have a hysteresis as a gate insulator layer, it is controlling the voltage between terminals applied to a memory device, and a reset of a memory device and the signal writing of memory are performed. As shown in drawing, in addition to the technique of connecting TFT 7 to a memory device, connection of a memory device is also possible by enhancement of a driving signal to the direct presentation electrode.

(Example 3) Although an alternating current signal is inputted only into Vcom (common electrode 8) and the liquid crystal material is driven in the 1st example, you may input an alternating current signal into Vref side (reference line 5). When an alternating current signal is inputted into Vref, change of the common electrode potential by the joint capacity of a reference line 5 and the common electrode 8 is observed through the liquid crystal layer 10. It is also possible for there to be a method of using the signal which reversed the sign of a driving signal every reference line 5, and to carry out the period of an alternating current driving signal for every scan time further as a cure of this change.

[0041] On the other hand, it is Vcom about an alternating current signal. Vref It inputs into both, and driving is also possible and low-battery-ization of the driver IC for driving signals of it is attained. This drive is Vcom. As compared with the case where an alternating current drive is carried out, the amount of currents which flows to one output terminal of a driver IC, or the voltage outputted becomes low, and it is enabled to lower the power which a driver IC consumes.

[0042] As a material which constitutes the barrier layer of the memory device in each example, although single crystal silicon, polycrystal silicon, and an amorphous silicon can be considered, if especially the display device of this structure is an element which can operate 3 terminal switching device, the ratio of the resistance at the time of opening and closing is 105. Although it is desirable that it is about [twice], even if it is about 100 times at the lowest, it is thought that enforcement is possible. Use of the amorphous silicon by which this was *****ed less than [an organic material, the low temperature of about 150 degrees C, or it] in the barrier layer also comes to be considered, and the constraint on the process of each material and the constraint on element structure are eased.

[0043] Moreover, with the element which reduced the phot ***** fee process, even if it is the element of the switch property with the former inadequate as a display device, a still high contrast display is obtained. Moreover, a miniaturization of a size is realizable by carrying out enhancement of the element 24 in drawing 2 (b) in a performance by technique, such as various annealing. It is also possible to set it as the alternating current signal by the side of the long period by which a flicker is seldom *****ed (- 10 seconds) on the other hand, if an electro-optics-material property does not usually carry out a degradation with the passage of time in the use domain in the liquid crystal of a display material.

(Example 4) The technique refreshed for a memory device is making a weighting the line which change has generated in the display screen as above-mentioned, and it has realized stopping other power consumption for a still picture display. Although this drive technique can constitute a part for a

mechanical component from enhancement of the conventional line sequential drive (the driving method which scans a scanning wiring sequentially), it is necessary to carry out the scan of the scanning wiring corresponding to the recognized animation fraction. Although it becomes low-power-ization to recognize an animation fraction correctly and to rewrite the signaling information of only the animation section from the effect of decreasing the number of scanning wirings simply, constituting of drive IC becomes complicated and elevation of power consumption will be caused on the contrary.

[0044] Then, a reduction of the power consumption of total drive IC can be aimed at by blocking the number of specification lines of the animation display section. the number of lines to block ***** -- 10-200 -- the number of scanning lines of 50-100 is desirably good The specification technique of the blocked line prepares an image memory in the input section of a picture signal, and outputs the block position and signal of the scan line section which detected and detected the animation fraction to drive IC. On the basis of this output, signal supply to the memory device corresponding to the animation display fraction is performed.

[0045] The power consumption of the memory to which having an image memory outside corresponds must be reduced compared with the power consumption of this display device. In an ideal, although it is necessary to have an image memory for every display pixel, an animation is simply detectable by performing the comparison with the pre-count data which have memorized the status signal of the same scan line, for example a fixed period or after sampling all one by one and counting a binary information.

[0046] Although it cannot recognize by this technique even if it is animation display when the total whose display pixel is an ON state is the same, in addition to above-mentioned technique, the decrement of the error of an animation recognition is sharply attained by the comparison which uses the sum of the blocked memory data of the scan line section. On the other hand, the count mistake generated in the thump ***** section and the counter section poses a problem by this counter formula. When there are many count mistakes, in order to recognize all to be an animation, the effect of this configuration circuit cannot be expected. Then, this problem is solvable by taking a count error into consideration beforehand at the time of a comparison.

[0047] How to make the weighting of a semipermanent display display as simplification technique is also considered in the configuration of the animation detecting element which acquires the information on an animation from an image memory and this memory information. Specifically, many of software of a personal computer etc. has the screen of the object for selection, or a functional display in many cases among the circumference section of the display screen. Many of screen display for this selection does not change in many cases. In such a case, since the field which does not have much animation display is beforehand known to typical software, it is enabled to lower the weighting of the refreshment of a scanning signal to the field.

[0048] When the viewing area with the high probability which is a still picture exists also about individual software, it also becomes possible to carry out a weighting by an user specifying the field. The technique of operation screens, such as PDA, preparing for the display side beforehand the weighting for which a screen is refreshed partly about the device which can to some extent be predicted, and specifying with switches, such as DIP-SW, is also possible.

[0049] Moreover, also in operation screens, such as a measuring equipment, etc., the field where the display status of a screen changes frequently becomes main [the fraction of the menu which carries out the fraction which displays a measurement result, and operation guidance]. In addition, since these measuring instruments etc. understand beforehand that only a display of a measurement result changes when an user does not operate a control panel, they will scan the screen corresponding to the fraction of a measurement result display, and should just perform signal supply to a memory device.

[0050] Also in this case, it can correspond by setup by the side of display. What is necessary is just to arrange the screen of animation display so that an animation display fraction may concentrate on the scan line which specialization followed since the effect of this equipment will become high, if there are few lines scanned by animation display still finely.

(Example 5) Drawing 9 is the 1-block outline circuit-arrangement view of the active matrix type LCD

concerning the 5th example of this invention.

[0051] Here, it is in the case of a 4 bit 16 gradation display. The block (i1-M, j1-N) of ij position when making the pixel block count of the whole display into MxN piece is shown. In a display of mainstream VGA specification, it is set to M= 640 and N= 480 with a personal computer now.

[0052] The AND gate Gij is formed in the intersection of address-line ADRS-Xi of the orientation of screen X, and address-line ADRS-Yi of the orientation of screen Y, and AND-gate G0ij - G3 ij are formed in each intersection of the output and four image data lines D0-D3. The output of AND-gate G0ij - G3 ij is connected to memory device M0ij-M3ij, it connects with the gate electrode of switching-transistor T0ij-T3ij, and the output of memory device M0ij-M3ij controls turning on and off of switching-transistor T0ij-T3ij. Another side is connected to 1st common potential line COM1 through the pixel electrode at liquid crystal P0ij-P3ij of a pixel for either the source of switching-transistor T0ij-T3ij, or the drain electrode.

[0053] In addition, not only a static type but a dynamic type which was used in the 1st example is sufficient as the memory device of this example, EEPROM is further sufficient as it and it can use various kinds of formulae.

[0054] If area of the pixel electrode corresponding to P0 is set to 1 as the area of a pixel electrode differs, respectively and is shown in drawing 10, twice and P2 have increased 4 times and P3 has increased [P1] 8 times. The other end of liquid crystal P0ij-P3ij of a pixel is connected to 2nd common potential line COM2 which is a common electrode. Between 1st common potential line COM1 and 2nd common potential line COM2, the liquid crystal drive power DRV of an alternating current is connected.

[0055] An operation of this example is as follows. Both 4-bit image data continues holding the status until address-line ADRS-Yj of address-line ADRS-Xi of the orientation of screen X and the orientation of screen Y is memorized by active time memory device M0ij-M3ij and is next chosen again. Although fixed alternating voltage (for example, TN liquid crystal currently used for general present **5 voltage of 10V amplitude of V) required for a drive of the used liquid crystal is impressed to a counterelectrode It is controlled [by which the above-mentioned driver voltage is impressed to liquid crystal P0ij-P3ij of a pixel / or or] by switching-transistor T0ij-T3ij restricted by this memory circuit M0ij-M3ij prepared for every pixel whether impression is carried out, and the desired display status is maintained.

[0056] Although a great portion of power was consumed by the charge and discharge of the internal equivalent capacity of a data-line drive circuit or a control circuit, or a data-line wiring capacity load, the high-speed charge and discharge of counterelectrode capacity, etc. in the conventional active matrix LCD Even if a display image does not change like before, it is not necessary to impress the signal which the fixed period inverted to the data line for an alternating current drive, and in this example, most power with which a data-line drive circuit and a control circuit are mostly consumed there for a idle state becomes so small that it can ignore. Although the power by which an only consumption is carried out becomes what is depended on a direct-current drive of a counterelectrode, this is the grade by which a flicker is not ****ed, for example, since the low frequency of 60Hz or less is enough, power consumption is conventionally reduced by 1/100 to about 1/1000 of the driving method.

[0057] This ground is explained below. Capacity Ccom of the whole counterelectrode It determines mostly by dielectric constant [of electrode area S and liquid crystal] epsilon, and gap d, and is set to $C_{com} = \epsilon S / d$, and, in the case of the LCD of a 10 inch class, the capacity is about 0.1-0.3 micro F. They are frequency fdrv and voltage Vdrv about this capacity. Power Pcom consumed by carrying out charge and discharge by alternating voltage $P_{com} = C_{com} \cdot f_{drv} \cdot V_{drv}^2$ It is given, and when it drives by 60Hz **5V, it is set very much to 0.15mW - 0.45mW to a parvus thing. In fact, although the power consumption by the leakage current in the leakage resistance and memory circuit of liquid crystal, or a drive circuit is added to it, the power consumption as whole is still stopped small about several 10mW from 1mW.

[0058] Furthermore, a pixel electrode is blocked for every predetermined number, and when the dimensions of the pixel electrode within the block differ, respectively, the digital multi-gradation display by the area modulation becomes easy as 1 block. The following problems when carrying out such an

area modulation display by the conventional driving method do not occur, but very high-definition display quality is obtained.

[0059] Although the level shift of the pixel potential which affects a display performance at the time of switching occurred by the drive conventionally by the parasitic capacitance which switching devices, such as TFT, have, when this amount of level shifts is determined by the partition ratio of the switching noise charge of the above-mentioned parasitic capacitance and pixel electrode capacitance and the dimensions of a pixel electrode differed, the amount of level shifts was difficult to differ for every pixel electrode and to make it harmless also by adjustment of counterelectrode potential, and area gradation was substantially impossible.

[0060] In this example, since the level shift by this switching noise charge disappears the first stage after a switching end through the leakage resistance of liquid crystal, it does not affect a display performance and the digital multi-gradation display by the area modulation is possible for it. Moreover, by this technique, since it is in ON or two off status in the state of a 1-pixel display of liquid crystal, also in the time of a halftone display, an angle of visibility is large and the very good display quality which neither display unevenness nor a flicker also has is obtained.

[0061] In addition, this invention is not limited to each example mentioned above. In the example, although liquid crystal was used as a display material layer, not only this but other materials can be used. For example, applying to EL, a plasma display, etc. is possible. Moreover, in the case of liquid crystal, it is possible not only a reflected type but to apply to a penetrated type. In addition, in the domain which does not deviate from the summary of this invention, it can deform variously and can carry out.

[Translation done.]

*** NOTICES ***

Japan Patent Office is not responsible for any damages caused by the use of this translation.

1. This document has been translated by computer. So the translation may not reflect the original precisely.
2. **** shows the word which can not be translated.
3. In the drawings, any words are not translated.

DESCRIPTION OF DRAWINGS

[An easy explanation of a drawing]

[Drawing 1] The element structure-section view and circuit-arrangement view showing the basic configuration of the active matrix type LCD concerning the 1st example.

[Drawing 2] The circuit-arrangement view showing the 1 pixel section configuration of the 1st example.

[Drawing 3] The circuit-arrangement view showing the modification of the 1st example.

[Drawing 4] The circuit-arrangement view showing the modification of the 1st example.

[Drawing 5] Drawing showing an example of the driving signal in the 1st example.

[Drawing 6] Drawing showing other examples of the driving signal in the 1st example.

[Drawing 7] The circuit diagram and the structure-section view of a memory device showing the 1 pixel section configuration of the active matrix type LCD concerning the 2nd example.

[Drawing 8] Drawing showing an example of the driving signal in the 2nd example.

[Drawing 9] The 1-block outline circuit-arrangement view of the active matrix type LCD concerning the 5th example.

[Drawing 10] Drawing showing the size and the example of arrangement of a pixel in 1 block.

[Drawing 11] The circuit-arrangement view showing the conventional active matrix type LCD.

[An explanation of a sign]

- 1 -- The 1st substrate
- 2 -- Pixel electrode
- 3 -- Scanning line
- 4 -- Signal line
- 5 -- Reference line
- 6 -- Memory device
- 7 -- Switching device
- 8 -- Counterelectrode
- 9 -- The 2nd glass substrate
- 10 -- Liquid crystal layer (display material layer)
- 21 -- Switching device
- 22, 23 -- Inverter element
- 24 -- Switching device

[Translation done.]

**This Page is Inserted by IFW Indexing and Scanning
Operations and is not part of the Official Record**

BEST AVAILABLE IMAGES

Defective images within this document are accurate representations of the original documents submitted by the applicant.

Defects in the images include but are not limited to the items checked:

- ☒ **BLACK BORDERS**
- ☐ **IMAGE CUT OFF AT TOP, BOTTOM OR SIDES**
- ☐ **FADED TEXT OR DRAWING**
- ☐ **BLURRED OR ILLEGIBLE TEXT OR DRAWING**
- ☐ **SKEWED/SLANTED IMAGES**
- ☐ **COLOR OR BLACK AND WHITE PHOTOGRAPHS**
- ☐ **GRAY SCALE DOCUMENTS**
- ☐ **LINES OR MARKS ON ORIGINAL DOCUMENT**
- ☐ **REFERENCE(S) OR EXHIBIT(S) SUBMITTED ARE POOR QUALITY**
- ☐ **OTHER: _____**

IMAGES ARE BEST AVAILABLE COPY.

As rescanning these documents will not correct the image problems checked, please do not report these problems to the IFW Image Problem Mailbox.